Compact Ultra-Efficient PMIC with Maximum Power Point Tracking for Single/Dual PV Cells

Features and Benefits

Cold start from 250 mV input voltage and 5 µW input power (typical)

- Fast start-up from source.

Maximum Power Point Tracking

- Matches various single/dual elements PV cells;
- Configurable MPPT ratios of 35%, 50% and from 60% to 90% by 5% steps;
- Constant impedance matching (QFN package only);
- Configurable MPPT sensing timing and period;
- MPPT voltage operation range from 120 mV to 1.50 V.

Selectable overdischarge and overcharge protection

- Supports various types of rechargeable batteries (LiC, Li-ion, LiPo, Li-ceramic pouch, etc.).

Ultra-low power idle mode

- Stored energy is preserved when no source available.

Shipping and shelf mode

- Prevents energy drain from battery when no source available (KEEP_ALIVE pin);
- Disables storage element charging (DIS_STO_CH pin).

Configuration pins or I²C

- Easy setup;
- Basic settings at start-up with configuration pins;
- Advanced configuration with I²C (Fast Mode Plus).

Average power monitoring

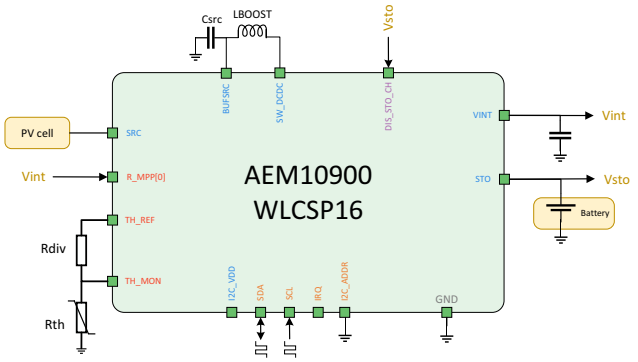
- Easy estimation of the charging power.

Integrated thermistor conditioning circuit

- Configurable battery thermal protection.

Applications

Wearable Electronics	Keyboards
Remote Control	Electronic Shelf Labels
Smart Buildings	Indoor Sensors



Description

The AEM10900 is a compact, fully integrated battery charger that harvests DC power to store energy in rechargeable batteries. It extends battery lifetime and removes the need for primary energy storage in a large range of applications.

Thanks to a Maximum Power Point Tracker and an ultra-low power boost converter, the AEM10900 harvests the maximum available power from a source to charge a storage element, such as a Li-ion battery or a LiC. The boost converter operates with input voltages ranging from 120 mV to 1.50 V, making AEM10900 ideal for single or dual element PV cell.

The AEM10900 has a unique cold-start circuit capable of operation with input voltages as low as 250 mV and power as minimal as 5 µW. The output voltages ranges from 2.8 V to 4.8 V, with configurable protection levels to prevent overcharging and overdischarging of the storage element. No external components are necessary to set these protection levels. Additionally, thermal monitoring safeguards the storage element, while an Average Power Monitoring system offers insights into the energy transfered to the storage element.

Thanks to the keep-alive feature, the AEM10900 internal circuit can stay powered by the storage element even in absence of a harvesting source. When keep-alive is disabled and no harvesting source is present, the AEM10900 turns off, preserving the energy of the storage element.

A shelf-mode can be obtained by disabling the keep-alive feature, preventing the battery to be drained during device storage. Furthermore, enabling the DIS_STO_CH feature creates a shipping mode by preventing battery charging.

The AEM10900 application schematic is featuring small PCB size (51 mm²) and a global lower bill of material, enabling small size and low cost implementation for single/dual element PV or pulsed sources versus other DCDC based solutions.

Device Information

Part Number	Package	Body size
10AEM10900D0000	WLCSP16-pin	2x2mm
10AEM10900C0000	QFN 28-pin	4x4mm

Evaluation Board

Part number
2AAEM10900D001 (WLCSP16)
2AAEM10900C001 (QFN28)

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Figure 1: Simplified schematic view

1. Introduction

The AEM10900 is a full-featured energy efficient battery charger able to charge a storage element (connected to STO) from an energy source (connected to SRC).

The core of the AEM10900 is a regulated switching converter (boost) with high-power conversion efficiency.

At first start-up, as soon as a required cold-start voltage of 250 mV and a sparse amount of power of at least 5 µW is available at the source (V_{STO} > V_{OVDIS}), the AEM10900 coldstarts. After the cold start, the AEM extracts the power available from the source if the input voltage is higher than 120 mV.

The AEM10900 can be fully configured through I²C (for both packages) or partially by configuration pins (depending on the package). I²C configuration is not mandatory, as the default configuration is made to fit the most common needs, along with the configuration pins for the most common settings (depending on the package).

Through I²C communication or through the configuration pins, the user can select a specific operating mode from a variety of modes that cover most application requirements without any dedicated external component. The battery protection thresholds (V_{OVCH} and V_{OVDIS}) can be configured with the help of the STO_CFG[2:0] pins (not available on WLCSP16 package). They can also be configured in 60 mV steps using the I²C bus.

The Maximum Power Point (MPP) ratio is configurable by the configuration pins (R_MPP[2:0] on QFN28 package, R_MPP[0] on WLCSP16) or by the I²C interface. It ensures an optimum biasing of the harvester to maximize power extraction. The user can select a specific MPP ratio from two values (WLCSP16 package) or from eight values (QFN28 package), set by the configuration pins. With the I²C interface, the user can select a ratio amongst 9 different values.

Depending on the harvester, it is possible to adapt the timing between two MPP evaluations and the open circuit duration with the I²C communication but also with the configuration pins T_MPP[1:0] for the QFN28 version. There is a range of eight timing pairs.

The AEM10900 features an optional temperature protection. It can be set through the I²C interface and allows to define a temperature range so that, when the ambient temperature is outside that range, battery charging is disabled. One additional resistor and one additional thermistor are needed for this feature.

The KEEP_ALIVE functionality sets the source from which the AEM10900 supplies its internal circuitry VINT. It can be supplied either from the harvester connected on SRC or from the battery connected to STO.

When KEEP_ALIVE is disabled, the AEM10900 internal circuitry is running as long as enough energy is available on SRC. If no energy is available on SRC, the internal voltage drops down to reset voltage and the AEM needs to go through a cold start before being able to charge the battery again. This is useful for applications with long periods without energy on SRC and when the I²C is not used. If the I²C communication is used, the AEM will need to be reconfigured after the cold-start. With this setting, only a dozen nA of quiescent current is taken from the storage element.

When KEEP_ALIVE is enabled, the AEM10900 is supplied by STO, the circuit stays in SUPPLY STATE or SLEEP STATE as long as the battery connected to STO is above the overdischarge threshold. It prevents losing the I²C configuration when energy harvesting is not occurring and offers faster reactivity as the AEM is not reset depending on the available energy on SRC.

2. Pin Configuration and Functions

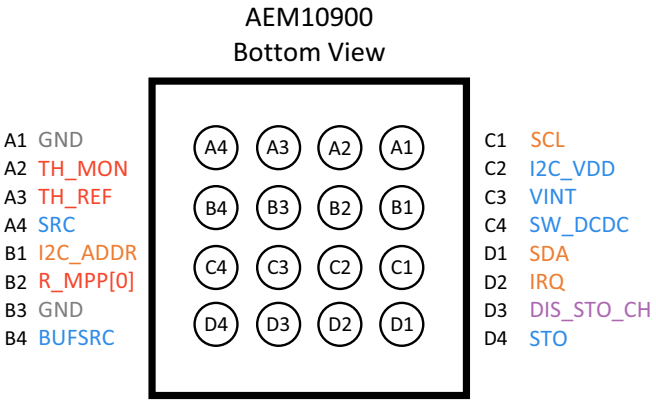

Figure 2: Pinout diagram WLCSP16

Name	Pin Number	Function
Power Pins		
SRC	A4	Connection to the harvested energy source.
BUFSRC	B4	Connection to an external capacitor buffering the boost converter input.
SWDCDC	C4	Switching node of the boost converter.
VINT	C3	Internal supply voltage.
I2C_VDD	C2	Connection to supply the I²C interface. - Connect to a 1.5 V to 2.2 V power supply if I²C is used. - Connect to GND if I²C is not used.
STO	D4	Connection to the energy storage element (rechargeable only). Cannot be left floating, voltage must always be above 2.5 V.
Configuration Pins		
TH_REF	A3	Reference voltage for thermal monitoring. Leave floating if not used.
TH_MON	A2	Pin for temperature monitoring. Connect to VINT is not used.
R_MPP[0]	B2	Used for the configuration of the MPP ratio. Read as HIGH if left floating.
Control pins		
DIS_STO_CH	D3	When HIGH, the AEM stops charging the battery. Read as LOW if left floating.
I²C Pins		
SDA	D1	Bidirectional data line. Connect to I2C_VDD if not used.

Table 1: Pins description WLCSP16

Name	Pin Number	Function
SCL	C1	Unidirectional serial clock for I²C. Connect to I2C_VDD if not used.
IRQ	D2	Output Interrupt request. Left floating if not used.
I2C_ADDR	B1	Configuration bit for I²C address. - If set HIGH, the address is 0x41. - If set LOW, the address is 0x40. Read as HIGH if left floating.
Other Pins		
GND	A1, B3	Ground connection, both terminals should be strongly tied to the PCB ground plane.

Table 1: Pins description WLCSP16

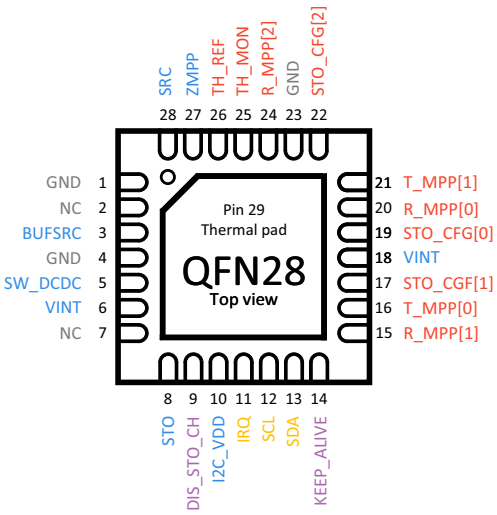

Figure 3: Pinout diagram QFN28

NAME	PIN NUMBER	Function
Power Pins		
SRC	28	Connection to the harvested energy source.
BUFSRC	3	Connection to an external capacitor buffering the boost converter input.
SWDCDC	5	Switching node of the boost converter.
VINT	6, 18	Internal supply voltage.
STO	8	Connection to the energy storage element (rechargeable only). Cannot be left floating, voltage must always be above 2.5 V.
I2C_VDD	10	Connection to supply the I²C interface. - Connect to a 1.5 V to 5.0 V power supply if I²C is used. - Connect to GND if I²C is not used.
ZMPP	27	Connection for R_{ZMPP} (Must be left floating or grounded when not used)
Configuration Pins		
STO_CFG[0]	19	Used for the configuration of the threshold voltages for the energy storage element. Read as HIGH if left floating.
STO_CFG[1]	17	
STO_CFG[2]	22	
T_MPP[0]	16	Used for the configuration of the MPP timings. Read as HIGH if left floating.
T_MPP[1]	21	
R_MPP[0]	20	Used for the configuration of the MPP ratio. Read as HIGH if left floating.
R_MPP[1]	15	
R_MPP[2]	24	
TH_REF	26	Reference voltage for thermal monitoring. Leave floating if not used.
TH_MON	25	Pin for temperature monitoring. Connect to VINT if not used.
Control Pins		
DIS_STO_CH	9	When HIGH, the AEM stops charging the battery. Read as LOW if left floating.
KEEP_ALIVE	14	When HIGH, the internal circuitry is supplied from STO. When LOW, the internal circuitry is supplied from SRC. Read as HIGH if left floating.

Table 2: Pins description QFN28

NAME	PIN NUMBER	Function
I²C Pins		
SDA	13	Bidirectional data line. Connect to I2C_VDD if not used.
SCL	12	Unidirectional serial clock for I²C. Connect to I2C_VDD if not used.
IRQ	11	Output Interrupt request. Leave floating if not used.
Other pins		
GND	1, 4, 23, 29 (thermal pad)	Ground connection, each terminal should be strongly tied to the PCB ground plane, pin 29 (thermal pad) being the main GND connection of the AEM10900.
NC	2, 7	Not connected pins, leave floating.

Table 2: Pins description QFN28

3. Specifications

3.1. Absolute Maximum Ratings

Parameter	Value
Voltage on SRC	2.0 V
Voltage on SWDCDC, STO, I2C_VDD, SDA, SCL, IRQ, DIS_STO_CH	5.5 V
Voltage on VINT, KEEP_ALIVE STO_CFG[2:0], R_MPP[2:0], T_MPP[1:0], TH_REF, I2C_ADDR, TH_MON	2.75 V
Operating junction temperature	-40°C to 125°C

Table 3: Absolute maximum ratings

ESD CAUTION	
	ESD (ELECTROSTATIC DISCHARGE) SENSITIVE DEVICE These devices have limited built-in ESD protection and damage may thus occur on devices subjected to high-energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality

3.2. Electrical Characteristics at 25 °C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Power Conversion						
$P_{SRC,CS}$	Minimum source power required for cold start[1]	During cold start AEM10900		2.47		µW
		During cold start AEM10901		3.99		µW
$V_{SRC,CS}$	Minimum source voltage required for cold start			0.25		V
V_{MPP}	Target regulation voltage on SRC when extracting power.		0.12		1.50	V
V_{OC}	Open-circuit voltage of the source				2.0	V
Timing						
T_{VOC}	Open-circuit duration for the MPP evaluations		See Table 7			ms
T_{MPPT}	Time between two MPP evaluations		See Table 7			s
$T_{STO,SUPPLY}$	Time between two V_{STO} evaluations in SUPPLY STATE			0.12		s
$T_{STO,SLEEP}$	Time between two V_{STO} evaluations in SLEEP STATE			0.96		s
$T_{GPIO,MON}$	Time between two GPIO state evaluations			1.92		s
$T_{TEMP,MON}$	Time between two temperature evaluations			7.67		s
T_{CRIT}	Time spent in SHUTDOWN STATE with V_{STO} below V_{OVDIS} before switching to OVDIS STATE			2.50		s
Storage Element						
V_{STO}	Voltage on the storage element		2.5		4.8	V
V_{OVCH}	Maximum voltage accepted on the storage element before disabling its charging		3	See section 6.4	4.8	V
V_{OVDIS}	Minimum voltage accepted on the storage element before stopping to supply VINT if Keep-alive is enabled.		2.8		4.05	V
Internal supply & Quiescent Current						
V_{INT}	Internal supply voltage	Auto-regulated, outside of reset and coldstart conditions.		2.2		V
$I_{QSUPPLY}$	Quiescent current on STO in SUPPLY STATE	V_{STO} = 3.7 V		242		nA
I_{QSLEEP}	Quiescent current on STO in SLEEP STATE	V_{STO} = 3.7 V		162		nA
I_{QSTO}	Quiescent current on STO when Keep-alive functionality is disabled			7.4		nA
I²C interface						
Bus frequency				400	1000	kHz
V_{I2C_VDD}	I²C interface supply pin voltage		1.5		5.0	V
SCL	I²C interface communication pins		Pull-up to I2C_VDD with resistors			
SDA						

Table 4: Electrical characteristics

1.These values are valid with the recommended BOM components (see Section 13)

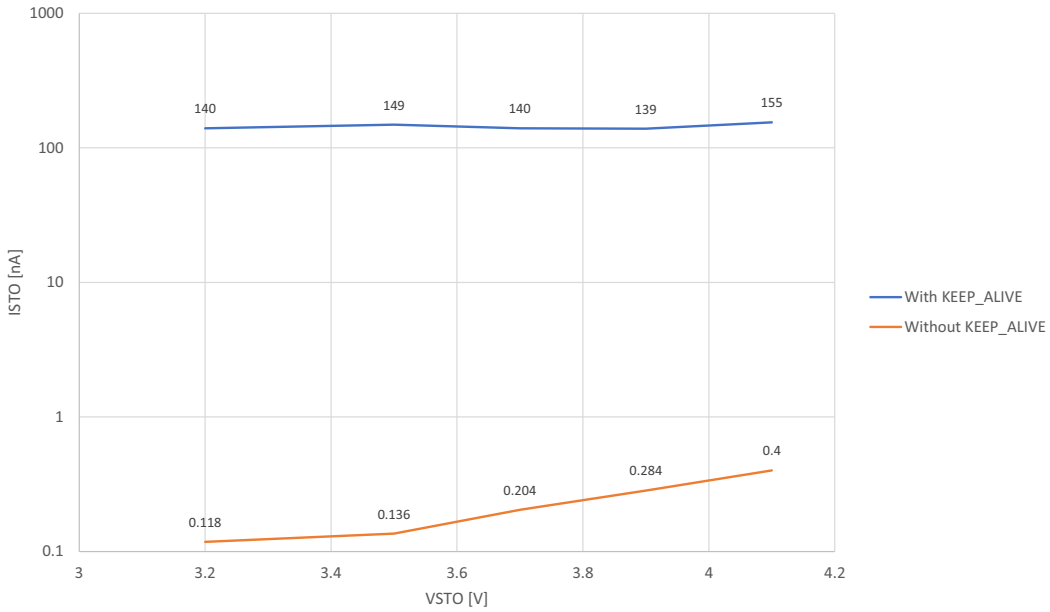

Figure 4: Quiescent current

3.3. Typical Characteristics

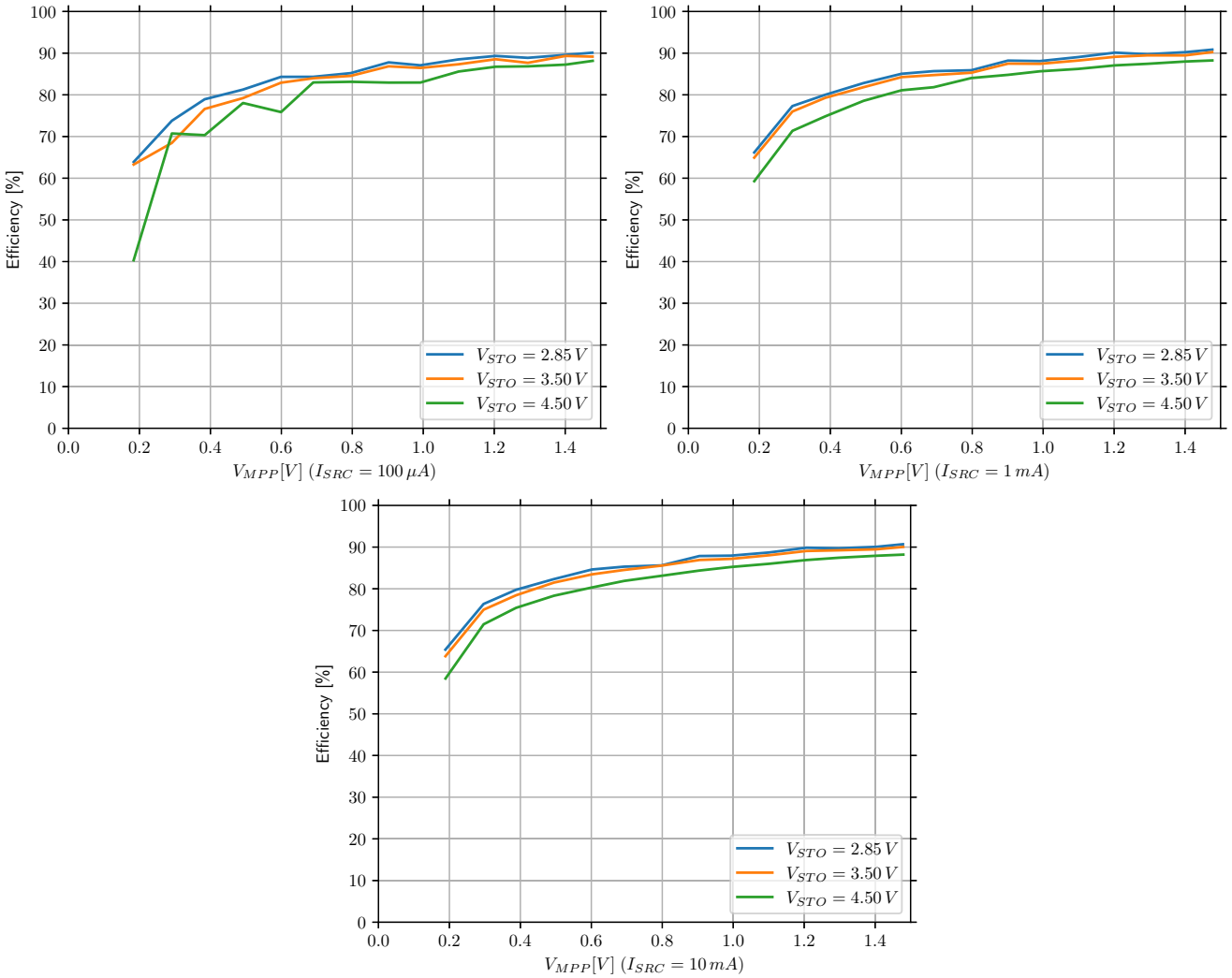

Figure 5: AEM10900 DCDC conversion efficiency (L_{DCDC}: TDK VLS252012HBX-6R8M-1)

3.4. Recommended Operation Conditions

Symbol	Parameter		Min	Typ	Max	Unit
External Components						
L_{DCDC}	Inductor of the boost converter		3.3	6.8		µH
C_{SRC}	Capacitor decoupling the BUFSRC terminal		10			µF
C_{INT}	Capacitor decoupling V_{INT}		3.3			µF
C_{STO}	Capacitor decoupling the STO terminal[1]		5	22		µF
R_{ZMPP}	Optional - Resistor for the ZMPPT configuration (see Section 6.3)		33		200 k	Ω
R_{DIV}	Optional - pull-up resistor for the thermal monitoring		5k	22k	33k	Ω
R_{TH}	Optional - NTC thermistor for the thermal monitoring	R0		10k		Ω
		Beta		3380		K
R_{SCL} / R_{SDA}	Optional - pull-up resistors for the I²C interface			1k		Ω
Logic input Pins						
R_MPP[2:0]	Configuration pins for the MPP ratio	Logic HIGH	Connect to VINT			
		Logic LOW	Connect to GND			
T_MPP[1:0]	Configuration pins for the MPP timings	Logic HIGH	Connect to VINT			
		Logic LOW	Connect to GND			
STO_CFG[2:0]	Configuration pins for the storage element thresholds	Logic HIGH	Connect to VINT			
		Logic LOW	Connect to GND			
KEEP_ALIVE	Configuration for the “keep-alive” functionality	Logic HIGH	Connect to VINT			
		Logic LOW	Connect to GND			
DIS_STO_CH	Configuration for disabling the charging of the battery	Logic HIGH	Connect to STO			
		Logic LOW	Connect to GND			

Table 5: Recommended operating conditions

1.Decoupling capacitor of at least 5µF is required to avoid damaging the AEM. The decoupling capacitor is to be sized according to the storage element internal resistance (ESR) to ensure optimal efficiency of the DCDC converter. It is recommended to use a capacitor of at least 22 µF when measuring the AEM10900 efficiency with laboratory equipment such as source measurement units (SMU). A battery must be connected to STO when a harvester is connected to the AEM to avoid damaging it.

4. Functional Block Diagram

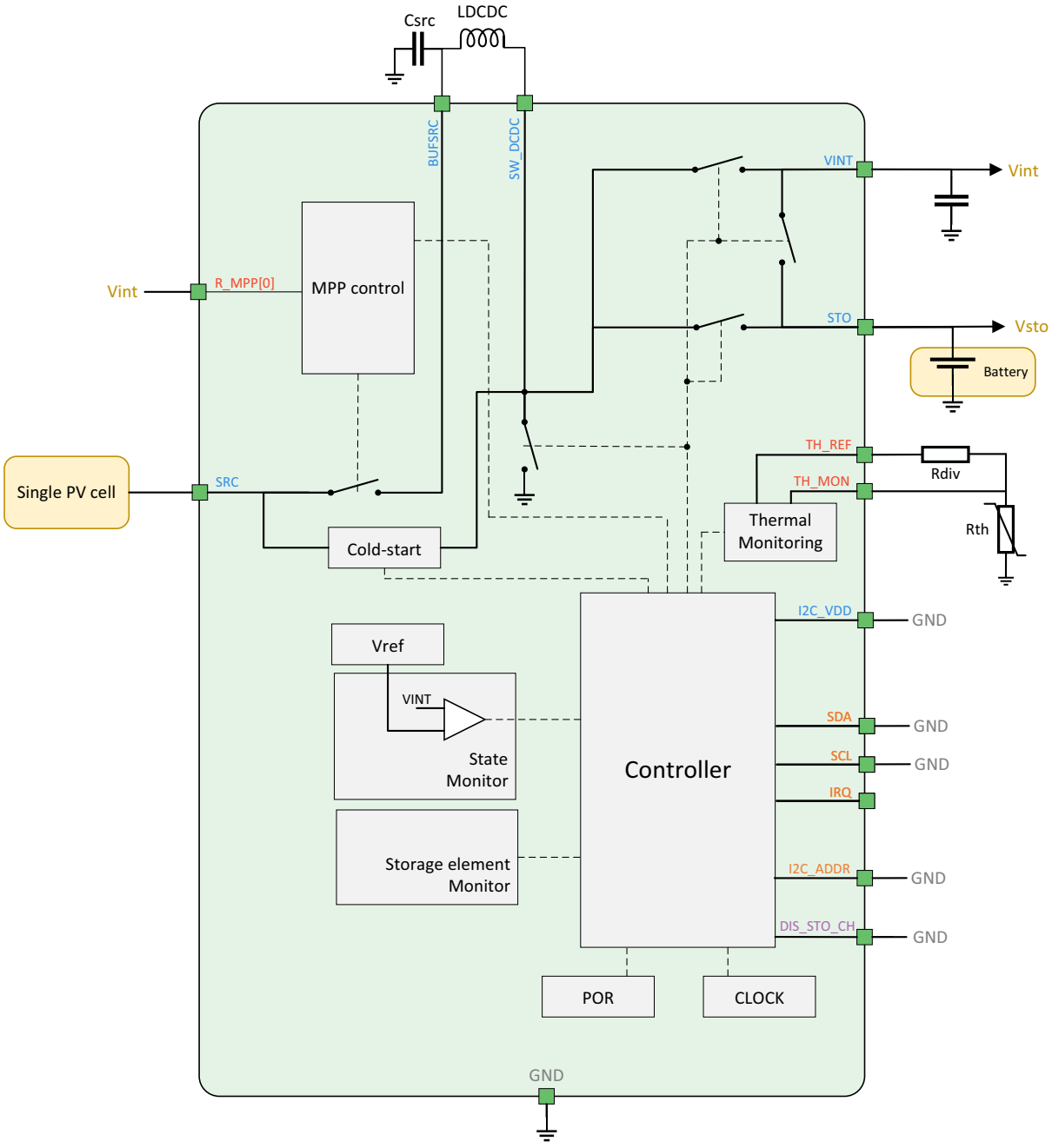

Figure 6: Functional block diagram (WLCSP16 package)

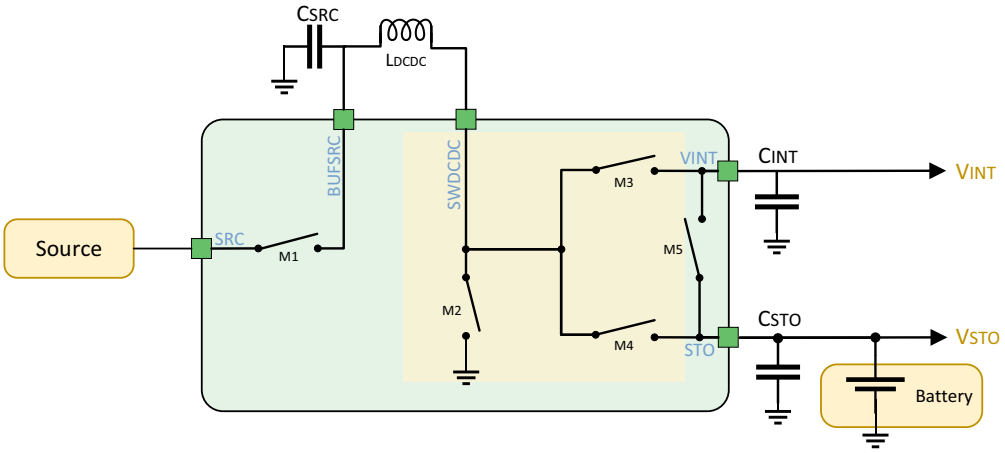

Figure 7: Simplified schematic view of the AEM10900

5. Theory of Operation

5.1. Boost Converter

The boost (step-up) converter raises the voltage available at BUFSRC to a level suitable for charging the storage element, in the range of 2.8 V to 4.8 V, according to the system configuration. The switching transistors of the boost converter are M2, M3 and M4. The reactive power component of this converter is the external inductor L_{DCDC}.

Periodically, the MPP control circuit disconnects SRC and BUFSRC pins (transistor M1) in order to measure the open-circuit voltage of the harvester and evaluate the input target voltage. BUFSRC is decoupled by the capacitor C_{SRC}, which smoothens the voltage against the current pulses induced by the boost converter.

The storage element is connected to the STO pin, whose voltage is V_{STO}. This node is linked to the output of one of the high-side transistors (M4) of the boost converter. When energy harvesting is occurring, the boost converter charges the battery. If VINT drops below its regulation value and if the Keep-alive functionality is disabled, the AEM uses M3 instead of M4 as the high-side transistor of the boost converter until VINT reaches its target plus a small hysteresis. If the Keep-alive functionality is enabled, VINT is instead supplied from STO by modulating the gate of M5. In that case M3 is never used.

5.2. Maximum Power Point Tracking

The AEM10900 has a Maximum Power Point Tracking (MPPT) module, that relies on the fact that, for several models of harvesters (typ. solar cells), the ratio between the maximum power point voltage (V_{MPP}) and the open circuit voltage (V_{OC}) is constant for a wide range of harvesting conditions. For a solar cell, that means that V_{MPP} / V_{OC} is constant for any lighting conditions, even though both voltages increase when luminosity increases.

The MPP ratio (V_{MPP} / V_{OC}) differs from one harvester model to the other. User must set the MPP ratio to match the specifications of the harvester model used and thus, maximize power extraction. This ratio is set by the I²C interface or with the configuration pins R_MPP[2:0] according to Table 6.

The MPPT module evaluates the open circuit voltage V_{OC} periodically to ensure optimal power extraction at any time. The sampling period T_{MPPT} and sampling duration T_{VOC} are set according to Table 7 by configuring the TIMING field in the MPPTCFG register or with the configuration pins T_MPP[1:0]. Every T_{MPPT}, the MPPT stops extracting power from the source, waits during T_{VOC} for the source to rise to its open circuit voltage, and measures V_{OC}. The AEM10900 supports multiple V_{MPP} levels in the range from 0.12 V to 1.47 V. It offers a choice of up to nine values for the V_{MPP} / V_{OC} ratio.

The MPPT module is always active except in RESET STATE.

5.3. Thermal Monitoring

Thermal monitoring allows to protect the storage element by disabling the charge of the storage element and setting the STATUS.TEMP register when the temperature is outside of the defined temperature range. Enabling this functionality requires the use of a resistor (R_{DIV}) and a thermistor (R_{TH}). See Figure 8 for external components connections. The TH_REF terminal allows a reference voltage to be applied to the resistive divider while TH_MON is the measuring point. An ADC is measuring the voltage on TH_MON between 0 and 1 V. The temperature evaluation is done periodically ($T_{TEMP,MON}$) to spare power. Information for the thermal monitoring is described in Section 9.4. Thermal monitoring is optional, if not used connect TH_MON to VINT and leave TH_REF floating.

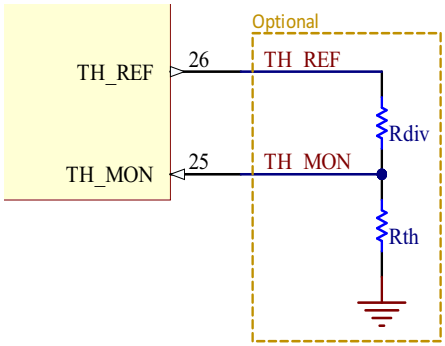

Figure 8: TH_REF and TH_MON connections

5.4. Average Power Monitoring

The Average Power Monitoring (APM) allows to evaluate the energy transfer from SRC to STO.

5.5. Automatic High-power Mode

When the AEM detects that the energy available on SRC is high enough, the boost converter automatically switches to high-power mode, increasing the harvesting current capability at the price of a slight efficiency degradation.

Preventing the AEM to switch to high-power mode may allow to use an inductor with half peak current rating for L_{DCDC} (see Section 6.6.2). On the other hand, allowing the AEM to switch to high-power mode increases the maximum current that the AEM can harvest from SRC to STO.

Automatic high-power mode is enabled by default and can be disabled by setting the PWR.HPEN to 0 through the I²C interface.

5.6. Keep-alive

The internal circuitry connected to VINT can be supplied either by SRC through the boost converter (keep-alive disabled), or by the battery STO (keep-alive enabled).

When the keep-alive feature is disabled, the AEM10900 is supplied from SRC. The AEM will switch to RESET STATE if the energy on SRC is not sufficient.

When the keep-alive feature is enabled, the AEM10900 is supplied from STO. VINT is regulated as long as $V_{STO} > V_{OVDIS}$. The keep-alive feature allows to maintain the I²C registers configuration and therefore preventing the loss of volatile memory. Referring to Table 4, the quiescent current is then $I_{QSUPPLY}$ or I_{QSLEEP}, depending on whether the AEM10900 is in SUPPLY STATE or in SLEEP STATE.

5.7. IRQ Pin

The IRQ pin allows user to get notified when various events happen (rising edge on IRQ pin). At start-up, the only flag that is enabled is I2CRDY, allowing user to know when the AEM10900 has finished to coldstart and thus, is out of RESET STATE and is ready to be programmed through I²C. Other flags can be enabled by writing the IRQEN register (Section 9.9). When the IRQ pin shows a rising edge, the flags can be determined by reading the IRQFLG register (Section 9.11). Reading the registers will reset the IRQ pin and clear the IRQFLG register.

5.8. State Description

Unless stated otherwise, all values given in this section are typical.

5.8.1. Reset State

In RESET STATE all nodes are deeply discharged and there is no available energy to be harvested. The AEM stays in this state until the source connected to SRC meets the cold start requirements long enough to make VINT rise up to 2.3 V. Cold start requirements depend on the AEM version and the L_{DCDC} inductor (see Figure 5 and Figure 10).

When VINT has reached 2.3 V, the AEM10900 reads the configuration pins and switches to SENSE SRC STATE.

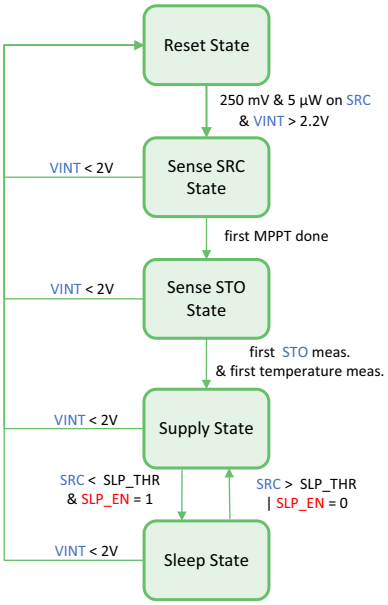

Figure 9: Diagram of the AEM10900 state machine

5.8.2. Sense SRC State

In SENSE SRC STATE, the AEM10900 does a first MPPT to evaluate the power available at SRC in order to be known as soon as possible the target regulation point. The MPPT is described in Section 5.2.

The next step is therefore to determine whether the battery can be charged. This mode is called SENSE STO STATE.

5.8.3. Sense STO State

In SENSE STO STATE the AEM10900 does the following measurements in order to know if the charging condition of the battery are met :

- Battery voltage on STO;
- Temperature through pins TH_MON and TH_REF (see Section 5.3. and 9.4.).

In this state, Once the measurements are done, AEM10900 switches to SUPPLY STATE.

5.8.4. Supply State

In SUPPLY STATE, the AEM transfers charges directly from to STO while maintaining V_{INT}.

If V_{INT} drops and the energy available on SRC is not sufficient to make V_{INT} rise again, there are two possible behaviors, depending on the 'keep-alive' feature:

- If keep-alive is enabled, VINT is supplied by the battery through M5, so the AEM10900 stays in SUPPLY STATE while energy is available on the battery;
- If keep-alive is disabled, VINT will no longer be maintained and the AEM switches to RESET STATE.

5.8.5. Sleep State

In SLEEP STATE, the AEM power consumption is reduced since the power available on the input is presumably low (V_{MPP} below the threshold voltage defined by the SLEEP.SRCTHRESH field). If the source voltage rises again above the threshold, or if the SLEEP.EN field is set to 0, the AEM10900 switches back to SUPPLY STATE.

SLEEP STATE is enabled by default with SLEEP.SRCTHRESHOLD at 105 V. STATUS.SRCTHRESH is asserted when V_{MPP} is set bellow this value.

6. System Configuration

6.1. Configuration Pins and I²C

6.1.1. Configuration Pins

After a cold start, the AEM10900 reads the configuration GPIOs. Those are then read periodically every 2 s, with the exception of the DIS_STO_CH pin that is read every 1 s. The configuration pins can be changed on-the-fly and the corresponding configuration will be updated at the next IO reading. The floating configuration pins are read as HIGH, except DIS_STO_CH which is read as LOW.

6.1.2. Configuration by I²C

To configure the AEM10900 through the I²C interface after a cold start, the user must wait for the IRQ pin to rise, showing that the AEM10900 is out of RESET STATE and is ready to communicate with I²C. The interrupt is reset by reading its register. Please note that the IRQ pin is always low during RESET STATE. See Section 9.11 for further informations about the IRQ pin.

Once IRQ goes HIGH, the user can then write to the desired registers and validate the configuration by setting the CTRL.UPDATE register field. All configuration pins are then ignored (with the exception of DIS_STO_CH, see Section 9.5) and all the configurations are set by the register values. All registers have a default value, that can be found in Table 9. It is possible to go back to the GPIO configuration by resetting the CTRL.UPDATE bit. To apply any modification to the configuration, simply change the wanted registers value and set the CTRL.UPDATE bit again.

Registers are stored in a volatile memory, so their value are lost when VINT drops below the reset voltage (2 V), making the AEM10900 switch to RESET STATE. Thus, when using the I²C configuration, it is highly recommended to enable the keep-alive (see section 9.5.). If keep-alive functionality is disabled, register configuration is lost every time the energy available on SRC is not sufficient to maintain V_{INT} above the reset voltage (2 V typical).

6.2. MPPT Configuration

Two parameters are necessary to configure the Maximum Power Point Tracking. The first parameter is the MPP tracking ratio, which is selected according to the characteristics of the input power source. This parameter is set on bits [3:0] of the MPPTCFG (0x01) register (see section 6.9.2), or by the configuration pins R_MPP[2:0] for the QFN28 package. On the WLCSP16 package, only R_MPP[0] is available as a configuration pin. The second parameter allows configuring the duration of the evaluation of V_{OC} (T_{VOC}) and the time between two MPP evaluations (T_{MPPT}). The configuration is set on bits [6:4] of the MPPTCFG (0x01) register (see section 6.9.2), or by the configuration pins T_MPP[1:0] for the QFN28 package. The T_{MPPT} configuration is only accessible through I²C on the WLCSP16 package.

Configuration	Availability Through Pins		MPPT ratio
R_MPP[3:0]	QFN28	WLCSP16[1]	Vmpp/Voc
LLL	yes	no	ZMPP
LLH	yes	no	90%
LHL	yes	no	65%
LHH	yes	no	60%
HLL	yes	no	85%
HLH	yes	no	75%
HHL	yes	yes	70%
HHH	yes	yes	80%

Table 6: Configuration of MPP ratio

1.On the WLCSP16 package, only the LSB is configurable.

Configuration	Availability Through Pins		Sampling duration [ms]	Sampling period [ms]
T_MPP[2:0]	QFN	WLCSP[1]	T_{VOC}	T_{MPPT}
HLL	yes	no	4	256
HLH	yes	no	2	128
HHL	yes	no	4	512
HHH	yes	yes	2	256

Table 7: Configuration of MPP timings

1.On the WLCSP16 package, the T_MPP[1:0] is not available, the default configuration is set to: T_MPP[HHH].

6.3. ZMPP Configuration

Instead of working at a ratio of the open-circuit voltage, the AEM10900 can regulate the input resistance of the boost converter so that it matches a constant resistance connected to the ZMPP pin (R_{ZMPP}). In this case, the AEM10900 regulates V_{SRC} at a voltage equal to the product of the ZMPP resistance and the current available at the SRC input.

This feature is not available for the WLCSP16 package.

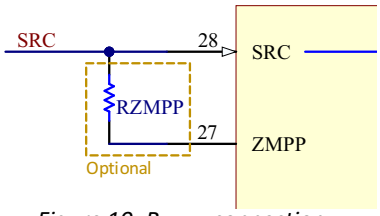

Figure 10: R_{ZMPP} connection

6.4. Storage Element Thresholds Configuration

The user must set the voltage thresholds for which the storage element is considered to be discharged (V_{OVDIS}) and fully charged (V_{OVCH}).

V_{OVDIS} is configured on the VOVDIS (0x02) register and encoded on 6 bits. The value to be written to the register is determined using the following equation:

$$THRESH = \frac{V_{OVDIS} - 0.50625}{0.05625}$$

THRESH is the integer value to be written in the register. The minimum value is 2.8 V. If the register value corresponds to V_{OVDIS} < 2.8 V, the threshold voltage is forced to 2.8 V.

V_{OVCH} is configured on the VOVCH (0x03) register and encoded on 6 bits. The value to be written to the register is determined using the following equation:

$$THRESH = \frac{V_{OVCH} - 1.2375}{0.05625}$$

THRESH is the integer value to be written in the register. The minimum value is 3.0 V. If the register value corresponds to V_{OVCH} < 3.0 V, the threshold voltage is forced to 3.0 V.

On the QFN28 package, it is also possible to configure V_{OVDIS} and V_{OVCH} with configuration pins STO_CFG[2:0] as shown in Table 8.

Configuration	Availability Through Pins			Storage element threshold		Battery type
STO_CFG[2:0]	I²C Interface	Configuration pins		V_{OVCH}	V_{OVDIS}	
		QFN28	WLCSP16			
LLL	yes	yes	no	4.50 V	3.30 V	NiCd 3 cells
LLH	yes	yes	no	4.00 V	2.80 V	Tadrian TLI1020A
LHL	yes	yes	no	3.63 V	2.80 V	LiFePO4
LHH	yes	yes	no	3.90 V	2.80 V	Tadrian HLC1020
HLL	yes	yes	no	3.90 V	3.50 V	Li-ion (ultra long life)
HLH	yes	yes	no	3.90 V	3.01 V	Li-ion (long life)
HHL	yes	yes	no	4.35 V	3.01 V	LiPo
HHH	yes	yes	yes	4.12 V	3.01 V	Li-ion/solid-state/ NiMH

Table 8: Usage of STO_CFG[2:0]

DISCLAIMER: the provided storage element thresholds in the table above are indicative to support a wide range of storage element variants. They are provided as is to the best knowledge of e-peas's application laboratory. They should not replace the actual values provided in the storage element manufacturer's specifications and datasheet.

6.5. Disable Storage Element Charging

Pulling up DIS_STO_CH to V_{STO} disables the charging of the storage element connected to STO. The storage element charging can also be disabled via I²C by setting the PWR.STOCHDIS register.

Please note that, if the keep-alive feature is enabled by pulling up KEEP_ALIVE to V_{INT}, VINT is supplied by STO regardless of the setting of DIS_STO_CH. To make sure that the storage element is neither charged nor used to supply VINT, user must tie both DIS_STO_CH to STO and KEEP_ALIVE to GND.

6.6. External Components

6.6.1. Storage Element

The storage element of the AEM10900 must be a rechargeable battery, which size should be chosen so that its voltage does not fall below V_{OVDIS} for longer than 2.5 s during current draw from the battery to the load connected on it. To keep the chip functionality, minimum voltage on STO pin shall remain above 2.8V.

The monitoring of the storage element is done periodically. It is therefore possible that the storage element may be overloaded if it is incorrectly sized.

It is mandatory to buffer the battery with a capacitor C_{STO} if the internal resistance of the battery is high, to ensure that the current pulled from the battery by the application circuit does not ever make the battery voltage fall below 2.8 V.

A minimal decoupling capacitor of 22 µF is recommended to obtain optimal DCDC converter efficiency when using high ESR battery, or when measuring efficiency using laboratory equipments such as source measurement units (SMU).

6.6.2. External Inductor Information

L_{DCDC}

The AEM10900 operates with one standard miniature inductor. L_{DCDC} must comply to the following:

- Peak current rating must be at least 1 A for a 3.3 µH inductor in high-power mode and 500 mA if high-power mode is disabled. Current rating decreases linearly when inductor value increases.
- Switching frequency must be at least 10 MHz.
- ESR as low as possible as it has a strong influence on DCDC efficiency.
- The recommended values for optimal efficiency is 6.8 µH.

6.6.3. External Capacitors Information

C_{SRC}

This capacitor acts as an energy buffer at the input of the boost converter. It prevents large voltage variations when the buck-boost converter is active. The recommended value is 10 µF.

C_{INT}

This capacitor acts as an energy buffer for the internal voltage supply. The minimum effective value is 3.3 µF. 22µF is recommended.

C_{STO}

This capacitor allows for buffering the current peaks of the boost converter output.

6.6.4. Optional External Components for Thermal Monitoring

The following components are required for the thermal monitoring:

- One resistor, typ. 22 kΩ ±20% (PNRC0402FR-0722KL)
- One NTC thermistor, typ. R0 = 10 kΩ ±5% and Beta = 3380 K ±3% (NCP15XH103J03RC)

6.6.5. Optional Pull-up Resistors for the I²C Interface

SDA and SCL must be pulled up by resistors (1 kΩ typical) if the I²C interface is used. The value must be determined according to the I²C mode used.

7. I²C Serial Interface Protocol

The AEM10900 uses I²C communication for configuration as well as to provide information about system status and measurement data. Communication requires a serial data line (SDA) and a serial clock line (SCL). A device sending data is defined as a transmitter and a device receiving data as a receiver. The device that controls the communication is called a master and the device it controls is defined as the slave.

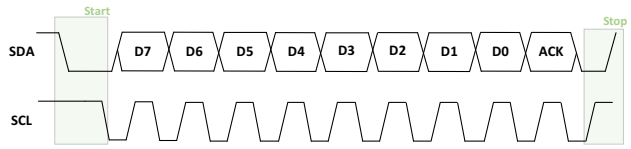

Figure 11: I²C transmission frame

The master is in charge of generating the clock, managing bus accesses and generating the start and stop bits. The AEM10900 is a slave that will receive configuration data or send the informations requested by the master.

The AEM10900 supports I²C Standard-mode (100 kHz maximum clock rate), Fast-mode (400 kHz maximum clock rate), and Fast-mode Plus (1 MHz maximum clock rate) device. Data are sent with the most significant bit first.

Here are some typical I²C interface states:

- When the communication is idle, both transmission lines are pulled up (SDA and SCL are open drain outputs);
- Start bit (S): to initiates the transmission, the master switches the SDA line low while keeping SCL high. This is called the start bit;
- Stop bit (P): to end the transmission, the master switches the SDA line from low to high while keeping SCL high. This is called a stop bit;
- Repeated Start bit (Sr): it is used as a back-to-back start and stop bit. It is similar to a start condition, but when the bus is not on idle;
- ACK: to acknowledge a transmission, the device receiving the data (master in case of a read mode transmission, slave in case of a write mode transmission) switches SDA low;
- NACK: when the device receiving data keeps SDA high after the transmission of a byte. When reading a byte, this can mean that the master is done reading bytes from the slave.

To initiate the communication, the master sends a byte with the following informations:

- Bits [7:1] is the slave address, which is 0x40 or 0x41 for the AEM10900, depending on the value of the I2C_ADDR pin. For packages where the I2C_ADDR pin is not present, the address is 0x41;
- Bit [0] is the communication mode: 1 for ‘read mode’ (used when the master reads informations from the slave) and 0 for ‘write mode’ (when the master writes informations to the slave);
- Slave replies with an ACK to acknowledge that the address has been successfully transmitted.

Here is the procedure for the master to write a slave register:

- Master sends the address of the slave in ‘write’ mode;
- Slave sends an ACK;
- Master sends the address of the register to be written. For example, for the TEMPCOLD register, the master sends the value 0x04;
- Slave sends an ACK;
- Master sends the data to write to the register;
- Slave sends an ACK;
- If the master wants to write register at the next address (TEMPHOT in our example), it sends next value to write, without having to specify the address again. This can be done several times in a row for writing several consecutive registers;
- Else the master sends a stop bit (P).

Here is the procedure for the master to read a slave register:

- Master sends the address of the slave in ‘write’ mode;
- Slave sends an ACK;
- Master sends the address of the register to be read. For example, for the MPPTCFG register, the master sends the value 0x01;
- Slave sends an ACK;
- Master sends a repeated start bit (Sr);
- Master sends the address of the slave in ‘read’ mode;
- Slave sends an ACK;
- Master provides the clock on SCL to allow the slave to shift the data of the read register on SDA;
- If the master wants to read register at the next address (VOVDIS in our example), it sends an ACK and provides the clock for the slave to shift its following 8 bits of data. This can be done several times in a row for reading several registers;

- If the master wants to end the transmission, it sends a NACK to notify the slave that the transmission is over, and then sends a stop bit (P).

Both communications are described in the Figure 12. Refer to Table 9 for all register addresses.

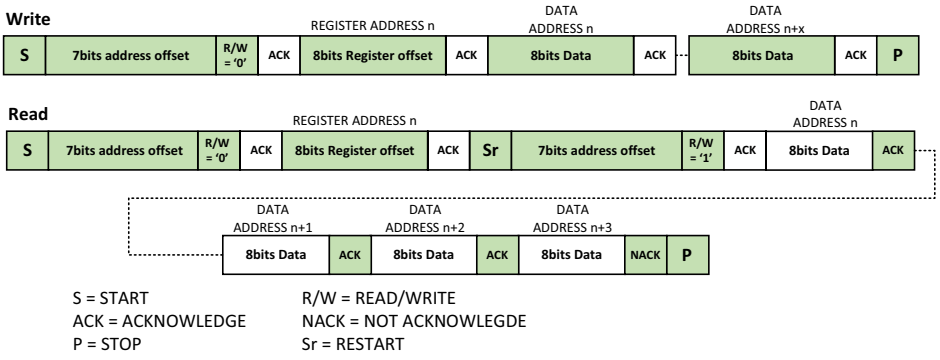

Figure 12: Read and write transmission

8. Registers Map

Address	Name	Bit	Field Name	Access	RESET	Description
0x00	VERSION	[3:0]	MINOR	R	-	Chip ID
		[7:4]	MAJOR			
0x01	MPPTCFG	[3:0]	RATIO	R/W	0x07 (80%)	MPPT ratio
		[6:4]	TIMING	R/W	0x07 (2ms/ 256ms)	MPPT timings
0x02	VOVDIS	[5:0]	THRESH	R/W	0x2D (3.05V)	Overdischarge level of the storage element
0x03	VOVCH	[5:0]	THRESH	R/W	0x33 (4.1V)	Overcharge level of the storage element
0x04	TEMPCOLD	[7:0]	THRESH	R/W	0x8F (0°C)	Cold temperature level
0x05	TEMPHOT	[7:0]	THRESH	R/W	0x2F (45°C)	Hot temperature level
0x06	PWR	[0:0]	KEEPALEN	R/W	0x01	Keepalive enable
		[1:1]	HPEN	R/W	0x01	high-power mode enable
		[2:2]	TMONEN	R/W	0x01	Temperature monitoring enable
		[3:3]	STOCHDIS	R/W	0x00	Battery charging disable
0x07	SLEEP	[0:0]	EN	R/W	0x01	Sleep mode enable
		[3:1]	SRCTHRESH	R/W	0x00	SRC LOW threshold
0x08	STOMON	[2:0]	RATE	R/W	0x00	ADC rate
0x09	APM	[0:0]	EN	R/W	0x00	APM enable
		[1:1]	RSVD1	R/W	0x00	Write 0x01 when APM is used
		[3:2]	RSVD2	R/W	0x00	Write 0x00 when APM is used
0x0A	IRQEN	[0:0]	I2CRDY	R/W	0x01	IRQ serial interface ready enable
		[1:1]	VOVDIS	R/W	0x00	IRQ STO OVDIS enable
		[2:2]	VOVCH	R/W	0x00	IRQ STO OVCH enable
		[3:3]	SRCTHRESH	R/W	0x00	IRQ SRC LOW enable
		[4:4]	TEMP	R/W	0x00	IRQ temperature enable
		[5:5]	APMDONE	R/W	0x00	IRQ APM done enable
0x0B	CTRL	[0:0]	UPDATE	R/W	0x00	Load I²C registers configuration
		[2:2]	SYNCBUSY	R	0x00	Synchronization busy flag
0x0C	IRQFLG	[0:0]	I2CRDY	R	0x00	IRQ serial interface ready flag
		[1:1]	VOVDIS	R	0x00	IRQ STOR OVDIS flag
		[2:2]	VOVCH	R	0x00	IRQ STOR OVCH flag
		[3:3]	SRCTHRESH	R	0x00	IRQ SRC LOW flag
		[4:4]	TEMP	R	0x00	IRQ temperature flag
		[5:5]	APMDONE	R	0x00	IRQ APM done flag
0x0D	STATUS	[1:1]	VOVDIS	R	0x00	Status STO OVDIS
		[2:2]	VOVCH	R	0x00	Status STO OVCH
		[3:3]	SRCTHRESH	R	0x00	Status SRC LOW
		[4:4]	TEMP	R	0x00	Status temperature
		[6:6]	CHARGE	R	0x00	Status STO CH
		[7:7]	BSTDIS	R	0x00	Status BST DIS GPIO
0x0E	APM0	[7:0]	DATA	R	0x00	APM data 0
0x0F	APM1	[7:0]	DATA	R	0x00	APM data 1
0x10	APM2	[7:0]	DATA	R	0x00	APM data 2
0x11	TEMP	[7:0]	DATA	R	0x00	Temperature data
0x12	STO	[7:0]	DATA	R	0x00	Battery voltage
0x13	SRC	[7:0]	DATA	R	0x00	SRC ADC value

Table 9: Register summary

9. Registers Configurations

9.1. Version Register (VERSION)

The VERSION register holds the version of the chip, with major and minor revision numbers.

VERSION Register	0x00	R
Bit [7:4]	Bit [3:0]	
MAJOR	MINOR	
0x00	0x00	

Table 10: VERSION register

Bit [7:4]: major revision number (VERSION.MAJOR).

Bit [3:0]: minor revision number (VERSION.MINOR).

9.2. MPPT Register (MPPTCFG)

The MPPT register MPPTCFG (0x01) is composed of 2 parts. The first part is reserved for the MPP ratio. This parameter is set on bits [3:0] of the register. The second part allows configuring the duration of the evaluation of V_{OC} and the time between two MPP evaluations (T_{MPPT}). The configuration is set on bits [6:4] of the register. All the information about the MPPT are available on section 5.2.

MPPTCFG Register	0x0B	R/W
Bit [7]	Bit [7:4]	Bit [3:0]
RESERVED	TIMING	RATIO
0	0x07	0x07

Table 11: MPPTCFG register

MPPTCFG.TIMING	T_{VOC} [ms]	T_{MPPT} [ms]
0x00	2	64
0x01	256	16384
0x02	64	4096
0x03	8	1024
0x04	4	256
0x05	2	128
0x06	4	512
0x07	2	256

Table 12: MPPTCFG.TIMING configuration

MPPTCFG.RATIO	R_MPP
0x00	ZMPP
0x01	90 %
0x02	65 %
0x03	60 %
0x04	85 %

Table 13: MPPTCFG.RATIO configuration

MPPTCFG.RATIO	R_MPP
0x05	75 %
0x06	70 %
0x07	80 %
0x08	35 %
0x09	50 %

Table 13: MPPTCFG.RATIO configuration

9.3. Storage Element Threshold Registers (VOVDIS, VOVCH)

The configuration of the storage element thresholds is done by setting two different registers through the I²C communication:

- The V_{OVDIS} threshold is configured in register VOVDIS (0x02);
- The V_{OVCH} threshold is configured in register VOVCH (0x03).

The information about the storage element threshold voltage is available on section 6.4.

9.4. Temperature Register (TEMPCOLD, TEMPHOT)

The configuration of the temperature thresholds is done by setting two registers through I²C communication:

- The low temperature threshold is configured in register TEMPCOLD (0x04);
- The high temperature threshold is configured in register TEMPHOT (0x05).

The temperature protection uses a voltage divider consisting of the resistor R_{DIV} and the thermistor $R_{TH}(T)$. Considering the specifications of the thermistor used, it is possible to determine the relationship between the temperature and the resistance of the thermistor. The following equation must therefore be applied to determine the value to be written to the register:

$$THRES = 256 \cdot \frac{R_{TH}(T)}{R_{TH}(T) + R_{DIV}}$$

The equation is the same for both the high and the low thresholds. THRESH is the value to be written to the registers, $R_{TH}(T)$ is the resistance of the thermistor at the threshold temperature and R_{DIV} is the resistance that creates a resistive divider with $R_{TH}(T)$, as shown on Figure 8. The AEM10900 determines if the ambient temperature is within the range previously set by measuring the voltage on pin TH_MON.

9.4.1. TEMPCOLD

Minimum temperature (cold) for storage element charging register.

TEMPCOLD Register	0x04	R/W
Bit [7:0]		
THRESH		
0x8F		

Table 14: TEMPCOLD register

The following equations are useful to determine the temperature from the THRES register field value:

$$R_{TH}(T) = R0 \cdot e^{B \cdot \left(\frac{1}{T} - \frac{1}{T_0}\right)}$$

$$T = \frac{B}{\ln\left(\frac{R_{TH}(T)}{R0}\right) + \frac{B}{T_0}}$$

- THRESH is the unsigned 8-bit value to be written in the registers to set the temperature threshold to the temperature T [K].
- R0 [Ω] is the resistance of the NTC thermistor at ambient temperature T_0 = 298.15 K (25 °C).
- $R_{TH}(T)$ [Ω] is the resistance of the thermistor at temperature T [K].
- T_0 [K] = 298.15 K (25 °C)
- T [K] is the current ambient temperature of the circuit.
- B is the characteristic constant of the thermistor, allowing to determine the resistance of the thermistor for a given temperature.

For example with a Murata NCP15XH103J03RC the default thresholds are 0°C and 45°C (see Table 9), which matches the specifications of most Li-Ion batteries.

Bit [7:0]: THRESH (TEMPCOLD.THRESH).

This fields is used to configure the minimum temperature (cold) threshold.

9.4.2. TEMPHOT

Maximum temperature (hot) for storage element charging register.

TEMPHOT Register	0x05	R/W
Bit [7:0]		
THRESH		
0x2F		

Table 15: TEMPHOT register

Bit [7:0]: THRESH (TEMPHOT.THRESH).

This fields is used to configure the maximum temperature (hot) threshold.

9.5. Power Register (PWR)

The PWR (0x06) register is dedicated to the power settings of the AEM10900 and is made of 4 bits:

PWR Register	0x06		R/W	
Bit [7:4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
RESERVED	STOCHDIS	TMONEN	HPEN	KEEPALEN
0x00	0	1	1	1

Table 16: PWR register

Bit [3]: Battery charging disable (PWR.STOCHDIS).

Prevent charging the battery.

- 0: DIS - allow the charging of the battery
- 1: EN - disable the charging of the battery.

The charging of the battery is disabled if either PWR.STOCHDIS is set or if the DIS_STO_CH pin is HIGH. The state of the DIS_STO_CH pin is not ignored when the AEM10900 switches to the I²C register configuration (see Section 6.1), as it would for all other configuration pins.

Bit [2]: Temperature monitoring enable (PWR.TMONEN).

The temperature monitoring enable bit enables the monitoring of the ambient temperature.

- 0: DIS - Disable the temperature monitoring.
- 1: EN - Enable the temperature monitoring.

Bit [1]: High-power mode enable (PWR.HPEN).

Allow the AEM to automatically enter high-power mode if needed, allowing for more power to be harvested from SRC (see section 5.5.).

- 0: DIS - Disable automatic high-power mode.
- 1: EN - Enable automatic high-power mode.

Bit [0]: Keep-alive enable (PWR.KEEPALEN).

Define the energy source from which the AEM10900 supplies VINT (internal circuitry).

- 0: DIS - VINT is supplied by SRC through the boost converter.
- 1: EN - VINT is supplied by STO.

Refer to section 5.6. for more information.

NOTE: disabling the keep-alive feature is not recommended when configuring the AEM10900 with I²C registers, see Section 5.6.

9.6. Sleep Register (SLEEP)

The Sleep register SLEEP (0x07) enables the sleep mode and sets the conditions for entering the sleep mode.

SLEEP Register	0x07	R/W
Bit [7:4]	Bit [3:1]	Bit [0]
RESERVED	SRCTHRESH	EN
0x00	0x00	1

Table 17: SLEEP register

SLEEP.SRCTHRESH	
Configuration	SRC threshold
0x00	V
0x01	0.202 V
0x02	0.255 V
0x03	0.300 V
0x04	0.360 V
0x05	0.405 V
0x06	0.510 V
0x07	0.600 V

Table 18: Configuration of the sleep threshold

Bit [3:1]: Sleep threshold (SLEEP.SRCTHRESH)

This field sets the voltage threshold below which the AEM10900 enters SLEEP STATE. Table 18 shows the available settings.

For example, if the SLEEP.SLPTHRESH field is set to 010, the AEM will switch to SLEEP STATE if the source voltage drops below 0.255 V at the MPP ratio (V_{MPP}).

Bit [0]: Sleep mode enable (SLEEP.EN)

This field controls the SLEEP STATE behavior of the AEM10900.

- 0: DIS - The AEM10900 will never switch to SLEEP STATE.
- 1: EN - Enable the AEM10900 to switch to SLEEP STATE if conditions are met (see below).

The SRC threshold is set by default at mV.

9.7. Storage Element Acquisition Rate Register (STOMON)

This field (STOMON, 0x08) configures the acquisition rate of the ADC that measures STO voltage. Depending on the application, the source and the storage element, the user might want to increase the frequency of the acquisitions of the battery voltage, so that the acquisition rate is significantly faster than the expected voltage variation on the battery. Increasing this frequency increases the energy consumption of the AEM10900.

STOMON Register (0x08)		
Configuration	Sampling rate	Additional consumption on storage element (typ.)
0x00	Every 1.024 s	0.4 nA
0x01	Every 512 ms	0.8 nA
0x02	Every 256 ms	1.6 nA
0x03	Every 128 ms	3.2 nA
0x04	Every 64 ms	6.4 nA

Table 19: Acquisition rates for STO ADC

9.8. Average Power Monitoring Control Register (APM)

Average Power Monitoring (APM; register address 0x09) allows for estimating the energy transferred from the source to the battery.

APM Register	0x09	R/W	
Bit [7:4]	Bit [3:2]	Bit [1]	Bit [0]
RESERVED	RSVD2	RSVD1	EN
0x00	0x00	0	0

Table 20: APM register

Bit [3:2]: Reserved 2 (APM.RSVD2)

Always write 0x00 to this register field when the APM is used.

Bit [1]: Reserved 1 (APM.RSVD1)

Always write 0x01 to this register field when the APM is used.

Bit [0]: APM enable (APM.EN)

This field enables the APM feature.

- 0: DIS - APM feature disabled.
- 1: EN - APM feature enabled.

9.9. IRQ Enable Register (IRQEN)

Interrupts enable register: configures on which event the IRQ pin is set HIGH.

IRQEN Register				0x0A		R/W	
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
RESERVED	APMERR	APMDONE	TEMP	SRCTHRESH	VOVCH	VOVDIS	I2CRDY
0	0	0	0	0	0	0	1

Table 21: IRQEN register

Bit [6]: IRQ APM error enable (IRQEN.APMERR)

Enable the IRQ pin to be asserted (HIGH) when an APM error occurs

- 0: DIS - Disable.
- 1: EN - Enable.

Bit [5]: IRQ APM done enable (IRQEN.APMDONE)

Enable the IRQ pin to be asserted (HIGH) when APM data is available.

- 0: DIS - Disable.
- 1: EN - Enable.

Bit [4]: IRQ temperature enable (IRQEN.TEMP)

Enable the IRQ pin to be asserted (HIGH) when the temperature crosses the minimum or maximum temperature allowed to charge the battery (see section 9.4.).

- 0: DIS - Disable.
- 1: EN - Enable.

Bit [3]: IRQ source low enable (IRQEN.SRCTHRESH)

Enable the IRQ pin to be asserted (HIGH) when V_{MPP} crosses the SRC LOW threshold.

- 0: DIS - Disable.
- 1: EN - Enable.

Bit [2]: IRQ storage overcharge enable (IRQEN.VOVCH)

Enable the IRQ pin to be asserted (HIGH) when the battery voltage crosses the V_{OVCH} threshold.

- 0: DIS - Disable.
- 1: EN - Enable.

Bit [1]: IRQ storage overdischarge enable (IRQEN.VOVDIS)

Enable the IRQ pin to be asserted (HIGH) when the storage element voltage crosses the V_{OVDIS} threshold.

- 0: DIS - Disable.
- 1: EN - Enable.

Bit [0]: IRQ serial interface ready enable (IRQEN.I2CRDY)

This bit is set at 1 by default.

When the AEM10900 has coldstarted and is ready to communicate through I²C. The IRQ pin is asserted (HIGH).

- 0: DIS - AEM10900 not ready to communicate through the I²C bus.
- 1: EN - AEM10900 ready to communicate through the I²C bus.

9.10. I²C Control (CTRL)

Control register.

CTRL Register	0x0B	R/W	
Bit [7:3]	Bit [2]	Bit [1]	Bit [0]
RESERVED	SYNCBUSY	RESERVED	UPDATE
0x00	0	0	0

Table 22: CTRL register

Bit [2]: SYNCBUSY (CTRL.SYNCBUSY).

This field indicates whether the synchronization from the I²C registers to the system registers is ongoing or not. While ongoing, it is not possible to write in the registers.

- 0: NSYNC - R: CTRL register not synchronizing.
- 1: SYNC - R: CTRL register synchronizing.

Bit [0]: UPDATE (CTRL.UPDATE).

This field is used to control the source of the AEM10900 configuration (GPIO or I²C).

Furthermore, this field is used to update the AEM10900 configuration with the current configuration from the I²C registers.

- 0: GPIO
  - W: load configurations from the GPIO.
  - R: configurations from the GPIO is currently used if read as 0.
- 1: I2C
  - W: load configurations from the I²C registers.
  - R: configurations from the I²C is currently used if read as 1.

NOTE: writing any register does not have any effect until 1 is written to the CTRL.UPDATE field, leading to the AEM10900 to read the new register values and apply them.

NOTE: when using I²C register configuration, user can switch back to GPIO configuration by writing 0 to the CTRL.UPDATE field. In that case, the settings previously written to the IRQEN registers are still valid even when using GPIO configuration, as well as the data in IRQFLG register.

9.11. IRQ Flag Register (IRQFLG)

The IRQFLG (0x0C) register contains all interrupt flags, corresponding to those enabled in the IRQEN register.

This register is reset when read.

IRQFLG Register				0x0C		R	
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
RESERVED	APMERR	APMDONE	TEMP	SRCTHRESH	VOVCH	VOVDIS	I2CRDY
0	0	0	0	0	0	0	1

Table 23: IRQFLG register

Bit [6]: IRQ APM error Flag (IRQFLG.APMERR)

This interrupt flag is set when an APM error occurred.

- 0: NFLG - No interrupt flag raised.
- 1: FLG - Interrupt flag raised.

Bit [5]: IRQ APM done Flag (IRQFLG.APMDONE)

This interrupt flag is set when APM data is available.

- 0: NFLG - No interrupt flag raised.
- 1: FLG - Interrupt flag raised.

Bit [4]: IRQ temperature Flag (IRQFLG.TEMP)

This interrupt flag is set when the temperature crosses the minimum or maximum temperature (selected through the TEMPCOLD and TEMPHOT registers).

- 0: NFLG - No interrupt flag raised.
- 1: FLG - Interrupt flag raised.

Bit [3]: IRQ source low Flag (IRQFLG.SRCTHRESH)

This interrupt flag is set when V_{MPP} crosses the SRC LOW voltage (selected through the SLEEP register).

- 0: NFLG - No interrupt flag raised.
- 1: FLG - Interrupt flag raised.

Bit [2]: IRQ storage overcharge Flag (IRQFLG.VOVCH)

This interrupt flag is set when the battery crosses the overcharge voltage (selected through the VOVCH register).

- 0: NFLG - No interrupt flag raised.
- 1: FLG - Interrupt flag raised.

Bit [1]: IRQ storage overdischarge Flag (IRQFLG.VOVDIS)

This interrupt flag is set when the battery crosses the overdischarge voltage (selected through the VOVDIS register).

- 0: NFLG - No interrupt flag raised.
- 1: FLG - Interrupt flag raised.

Bit [0]: IRQ serial interface ready Flag (IRQFLG.I2CRDY)

This interrupt flag is set when the AEM10900 has coldstarted and is ready to communicate through I²C (the corresponding interrupt source is enabled by default).

- 0: NFLG - No interrupt flag raised.
- 1: FLG - Interrupt flag raised.

9.12. Status Register (STATUS)

The STATUS (0x0D) register contains informations about the status of the AEM10900.

STATUS Register				0x0D		R	
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
BSTDIS	CHARGE	RESERVED	TEMP	SRCTHRESH	VOVCH	VOVDIS	RESERVED
0	0	0	0	0	0	0	0

Table 24: Status register

Bit [7]: Status BSTDIS (STATUS.BSTDIS)

This status indicates whether the storage charging is enabled or not via the GPIO. If this bit is set to 0, the storage element charging is enabled. If it is set to 1, the storage element charging is disabled.

Bit [6]: Status STO CH (STATUS.CHARGE)

This status indicates whether the AEM is currently charging the battery or not. If this bit is set to 0, the boost is running. If it is set to 1, the boost is not running.

Set condition:

$$(V_{STO} < V_{OVCH}) \ \& \ \overline{\text{STATUS.TEMP}} \ \& \ \overline{\text{STATUS.BSTDIS}}$$

$$\& \ (\text{OVDIS STATE} \mid \text{SUPPLY STATE} \mid \text{SHUTDOWN STATE})$$

Bit [4]: Temperature Status (STATUS.TEMP)

This bit is set to 1 if the ambient temperature is outside the range defined by the TEMPCOLD and TEMPHOT registers. It is set to 0 is the temperature is within this range.

Bit [3]: Status SRC LOW (STATUS.SRCTHRESH)

This status indicates whether the source voltage is higher or lower than the sleep level threshold. If the source voltage is higher than the sleep level then the field is set to 0, else the field is set to 1.

Bit [2]: Status STOR OVCH (STATUS.VOVCH)

This status indicates whether the battery voltage is higher or lower than the overcharge level threshold. If the battery voltage rises above V_{OVCH} then the field is set to 1, else it is set to 0.

Bit [1]: Status STOR OVDIS (STATUS.VOVDIS)

This status indicates whether the battery is higher or lower than the overdischarge level threshold. If the battery voltage goes below V_{OVDIS} then the field is set to 1, else it is set to 0.

9.13. Average Power Monitoring Data Registers (APM)

The APM (0x0E, 0x0F, 0x10) registers contain the Average Power Monitoring data.

APM0 Register (0x0E)							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
DATA[7:0]							

APM1 Register (0x0F)							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
DATA[15:8]							

APM2 Register (0x10)							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
SHIFT[3:0]				DATA[19:16]			

Table 25: APM registers

9.14. Temperature Data Register (TEMP)

This field contains the result of the ADC acquisition for the temperature monitoring. The voltage at the terminals of the voltage divider can be derived by applying the following equation, with V_{REF} = 1 V:

$$V_{TH} = \frac{V_{REF} \cdot DATA}{256}$$

Or, in order to make a comparison with the Table in the thermistor datasheet, it is possible to find the impedance of the thermistor:

$$R_{TH} = R_{DIV} \cdot \frac{DATA}{256 - DATA}$$

TEMP Register	0x11	R
Bit [7:0]		
DATA		
0x00		

Table 26: TEMP register

9.15. Battery Voltage Register (STO)

The STO (0x12) contains the 8-bit result from the ADC acquisition of the battery voltage. To convert the result to Volts, the following equation is applied.

$$V_{STO} = \frac{4.8\ V \cdot DATA}{256}$$

STO Register	0x12	R
Bit [7:0]		
DATA		
0x00		

Table 27: STO register

9.16. Source Voltage Register (SRC)

The SRC (0x13) register contains data reflecting the voltage level at which the input of the AEM10900 is regulated, resulting from the MPPT evaluation. To convert this value in Volts refer to Table 41.

SRC .DATA [7:0]	V_{MPP} [V]	SRC .DATA [7:0]	V_{MPP} [V]	SRC .DATA [7:0]	V_{MPP} [V]	SRC .DATA [7:0]	V_{MPP} [V]
0x06	0.112	0x14	0.345	0x22	0.765	0x30	1.185
0x07	0.128	0x15	0.375	0x23	0.795	0x31	1.215
0x08	0.142	0x16	0.405	0x24	0.825	0x32	1.245
0x09	0.158	0x17	0.435	0x25	0.855	0x33	1.275
0x0A	0.172	0x18	0.465	0x26	0.885	0x34	1.305
0x0B	0.188	0x19	0.495	0x27	0.915	0x35	1.335
0x0C	0.203	0x1A	0.525	0x28	0.945	0x36	1.365
0x0D	0.217	0x1B	0.555	0x29	0.975	0x37	1.395
0x0E	0.233	0x1C	0.585	0x2A	1.005	0x38	1.425
0x0F	0.247	0x1D	0.615	0x2B	1.035	0x39	1.455
0x10	0.263	0x1E	0.645	0x2C	1.065	0x3A	1.485
0x11	0.278	0x1F	0.675	0x2D	1.095		
0x12	0.292	0x20	0.705	0x2E	1.125		
0x13	0.315	0x21	0.735	0x2F	1.155		

Table 28: Source MPP Voltage register

10. Typical Application Circuits

10.1. Example Circuit 1

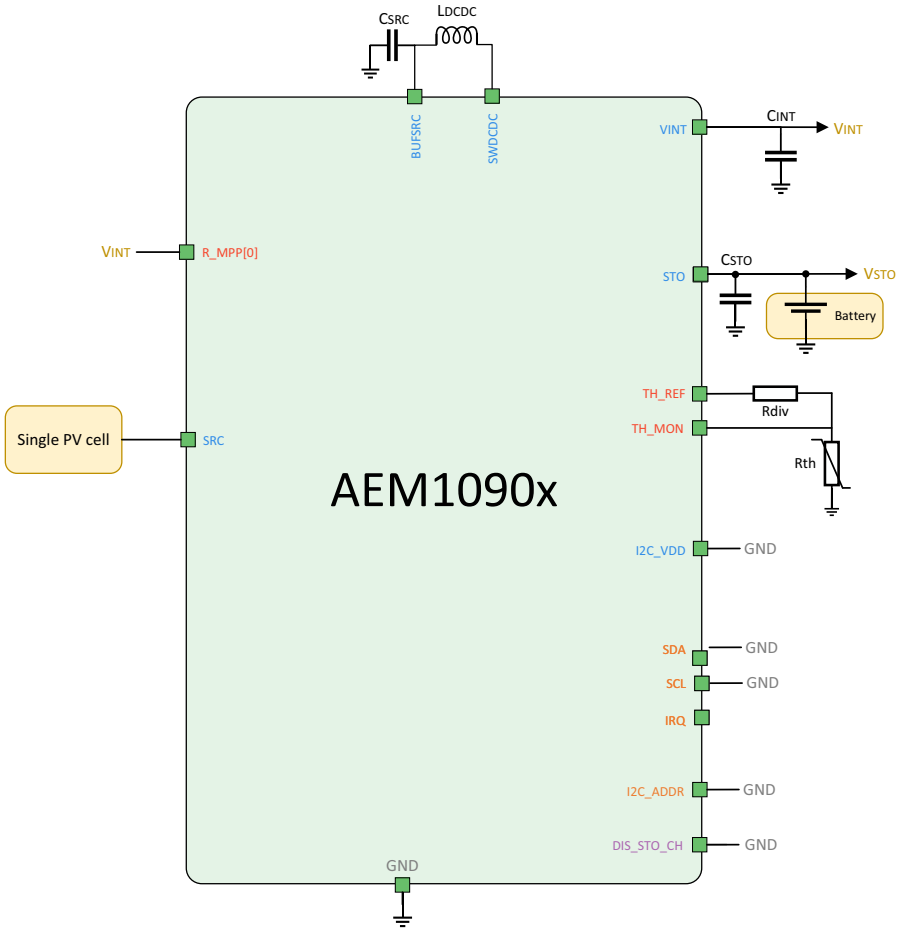

Figure 13: Typical application circuit 1 (WLCSP16 package)

The circuit is an example of a system with solar energy harvesting with the AEM10900 (WLCSP16 package). It uses a Li-ion rechargeable battery as energy storage.

- Energy source: PV cell.
- R_MPP[0]: The MPP ratio is set to 80%
- V_{OVCH} = 4.12 V
- V_{OVDIS} = 3.01 V
- The thermal monitoring is used with a default threshold value (TEMPCOLD = 0°C, TEMPHOT = 45°C) with R_{DIV} = 22 kΩ and R_{TH}: NCP15XH103J03RC.
- The I²C communication is not used.
- DIS_STO_CH is connected to GND: The charging of the storage element on STO is enabled.

10.2. Example Circuit 2

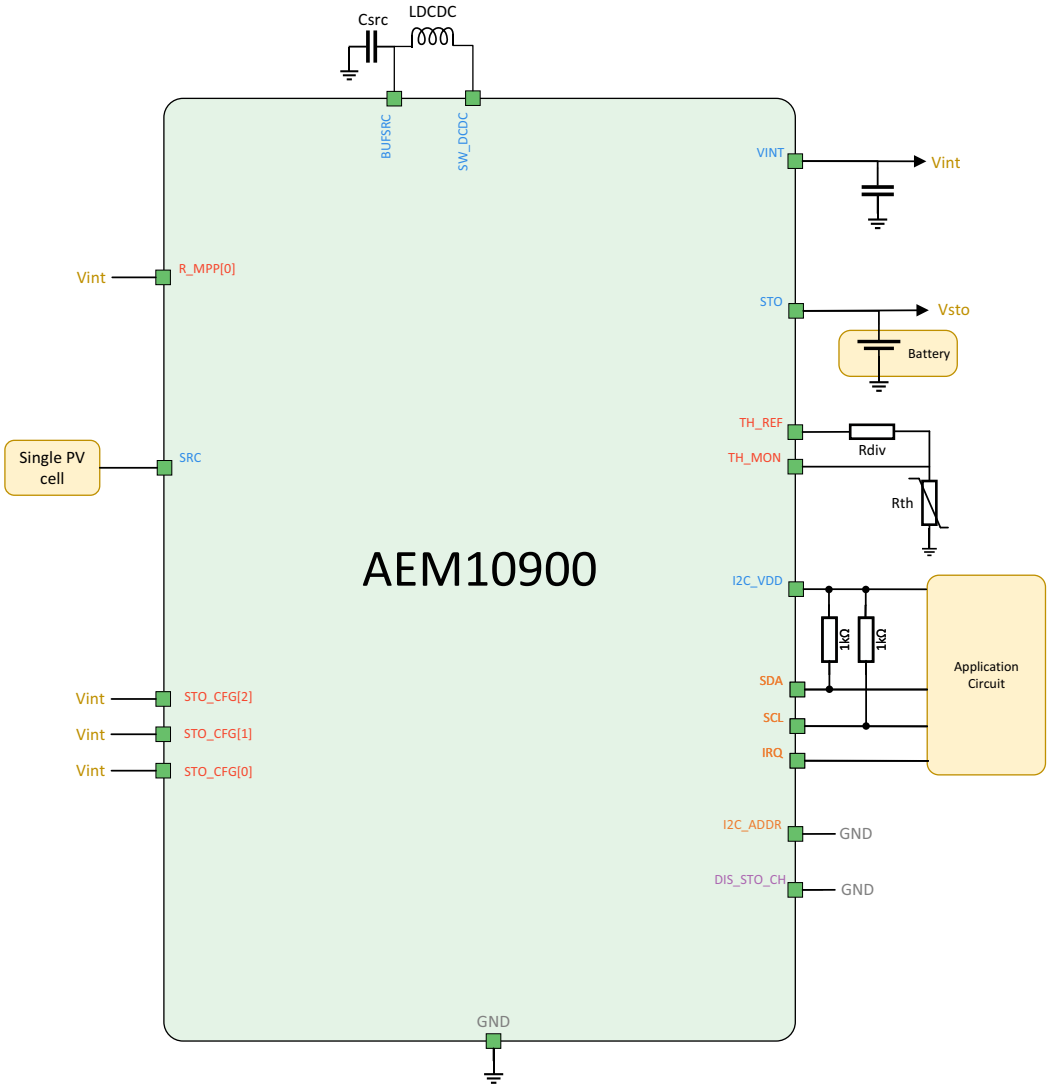

Figure 14: Typical application circuit 2 (WLCSP16 package)

The circuit is a example of a system with solar energy harvesting with the AEM10900 (QFN28 package). It uses a NiCd 3 cells battery as storage element.

- Energy source: PV cell
- R_MPP[2:0]: Configured through the I²C communication (MPP ratio = 90%)
- T_MPP[1:0]: Configured through the I²C communication (MPP timing = 2ms/128ms)
- STO_CFG[2:0]: Configured through the I²C communication
  - V_{OVCH} = 4.12 V
  - V_{OVDIS} = 3.30 V
- The thermal monitoring is used and the thresholds are configured through the I²C communication (Cold threshold = 10°C, Hot threshold = 60°C with R_{DIV} = 22 kΩ and R_{TH}: NCP15XH103J03RC).
- DIS_STO_CH is connected to GND: The charging of the storage element on STO is enabled.

Register Address	Register Name	Value
0x01	MPPTCFG	0101 0001
0x02	VOVDIS	0011 0010
0x03	VOVCH	0011 0011
0x04	TEMPCOLD	0111 0100
0x05	TEMPHOT	0001 1111

Table 29: Typical application circuit 2 register settings

NOTE: a configuration tool is available on e-peas website. It helps the user to read and write registers.

11. Circuit Behavior

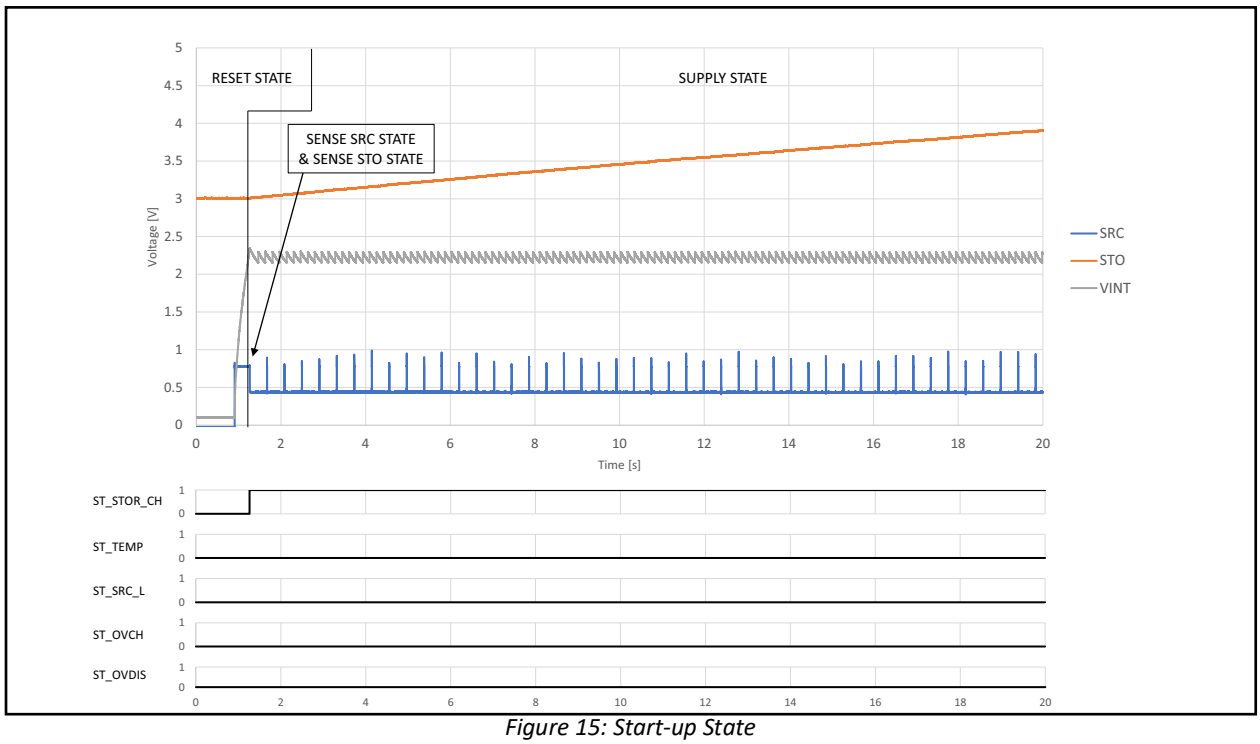

Figure 15: Start-up State

STO_CFG[2:0] = HHH, R_MPP[2:0] = LHH, T_MPP[1:0] = HL, storage element: capacitor (10 mF) pre-charged to 3V, SRC: current source 5 mA with voltage compliance (0.8 V), DIS_STO_CH = GND, KEEP_ALIVE = H.

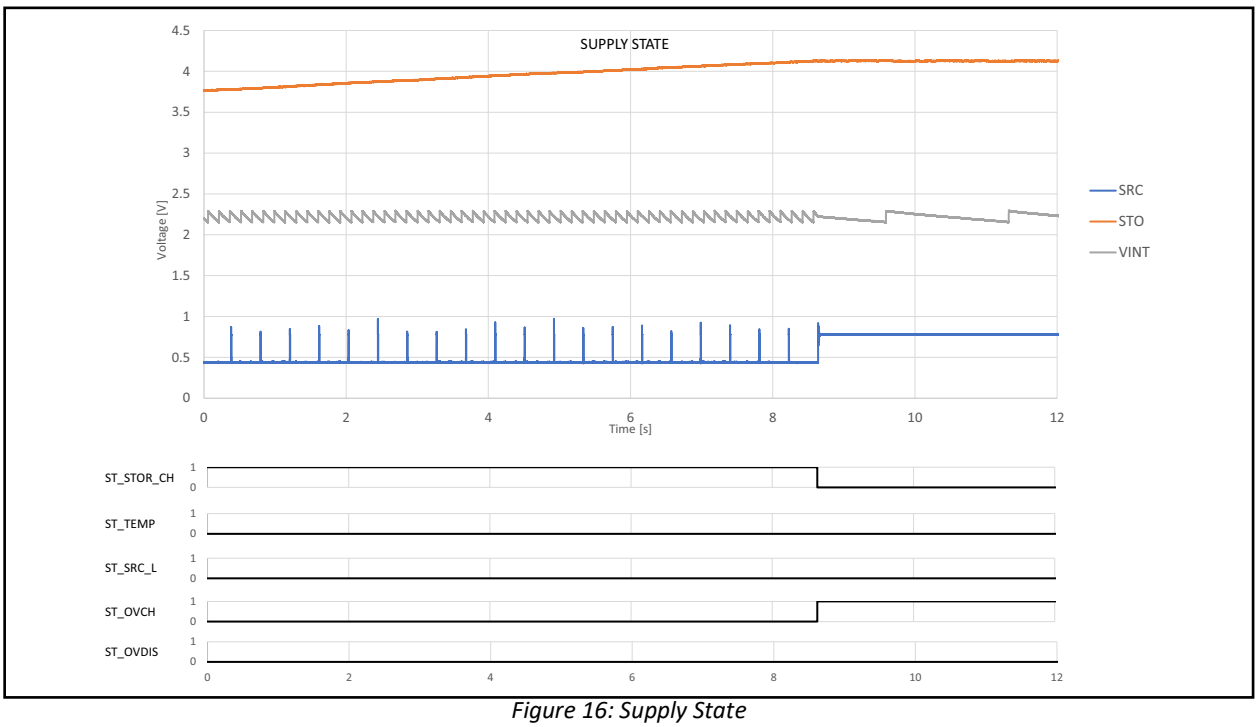

Figure 16: Supply State

STO_CFG[2:0] = HHH, R_MPP[2:0] = LHH, T_MPP[1:0] = HL, storage element: capacitor (10 mF) pre-charged to 3 V, SRC: current source 5 mA with voltage compliance (0.8 V), DIS_STO_CH = GND, KEEP_ALIVE = H.

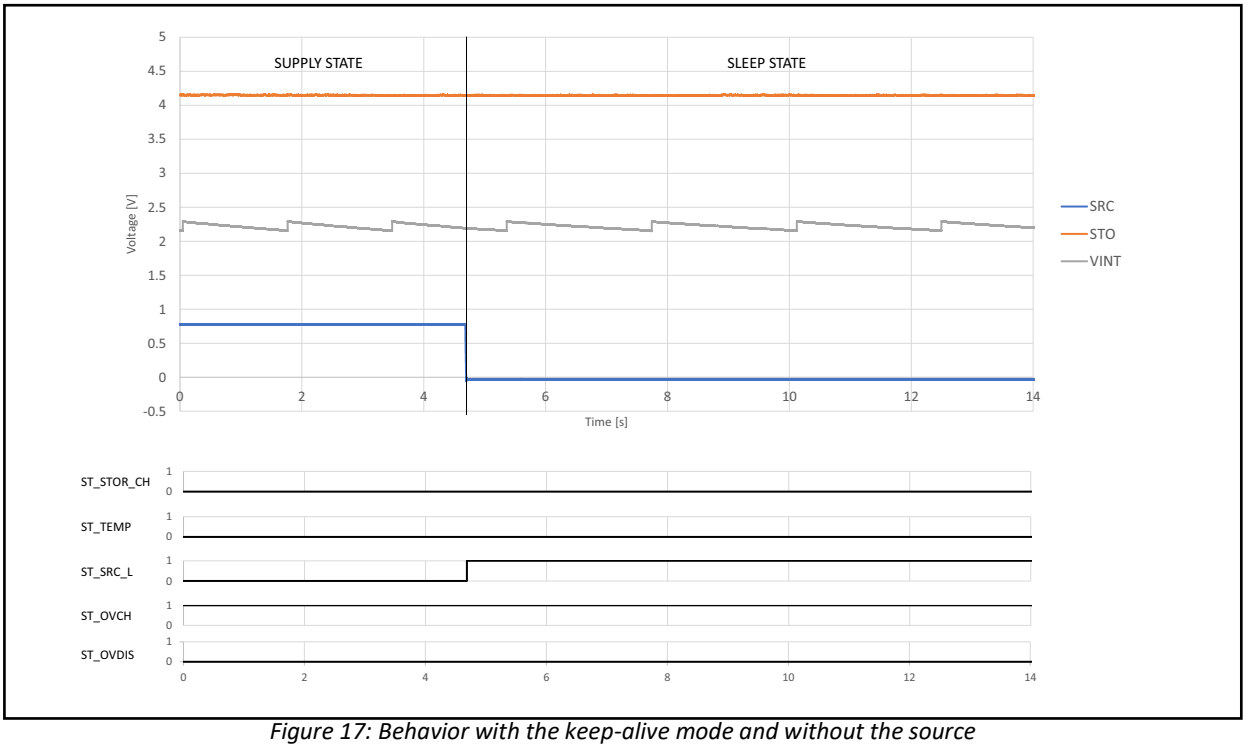

Figure 17: Behavior with the keep-alive mode and without the source

STO_CFG[2:0] = HHH, R_MPP[2:0] = LHH, T_MPP[1:0] = HL, storage element: capacitor (10 mF) pre-charged to 3 V, SRC: current source 5 mA with voltage compliance (0.8 V)(stop after ~4.5sec), DIS_STO_CH = GND, KEEP_ALIVE = H.

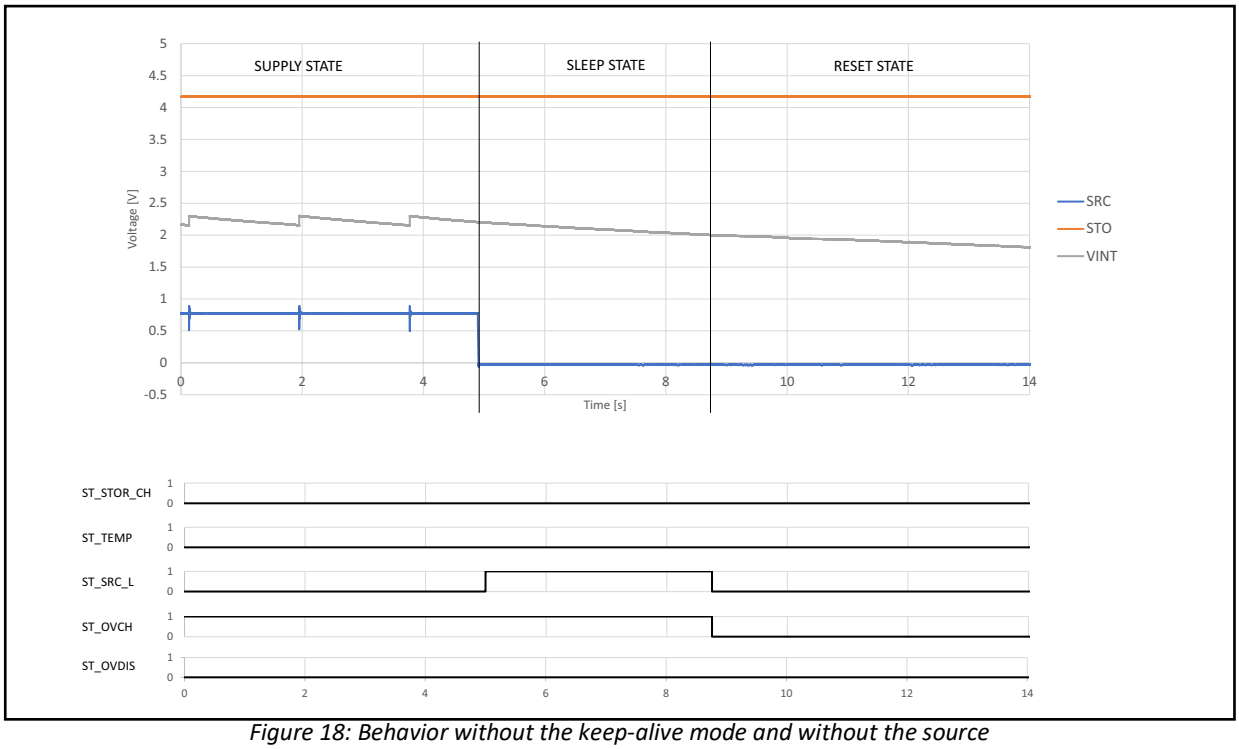

Figure 18: Behavior without the keep-alive mode and without the source

STO_CFG[2:0] = HHH, R_MPP[2:0] = LHH, T_MPP[1:0] = HL, storage element: capacitor (10 mF) pre-charged to 3 V, SRC: current source 5 mA with voltage compliance (0.8 V)(stop after ~5 sec), DIS_STO_CH = GND, KEEP_ALIVE = L.

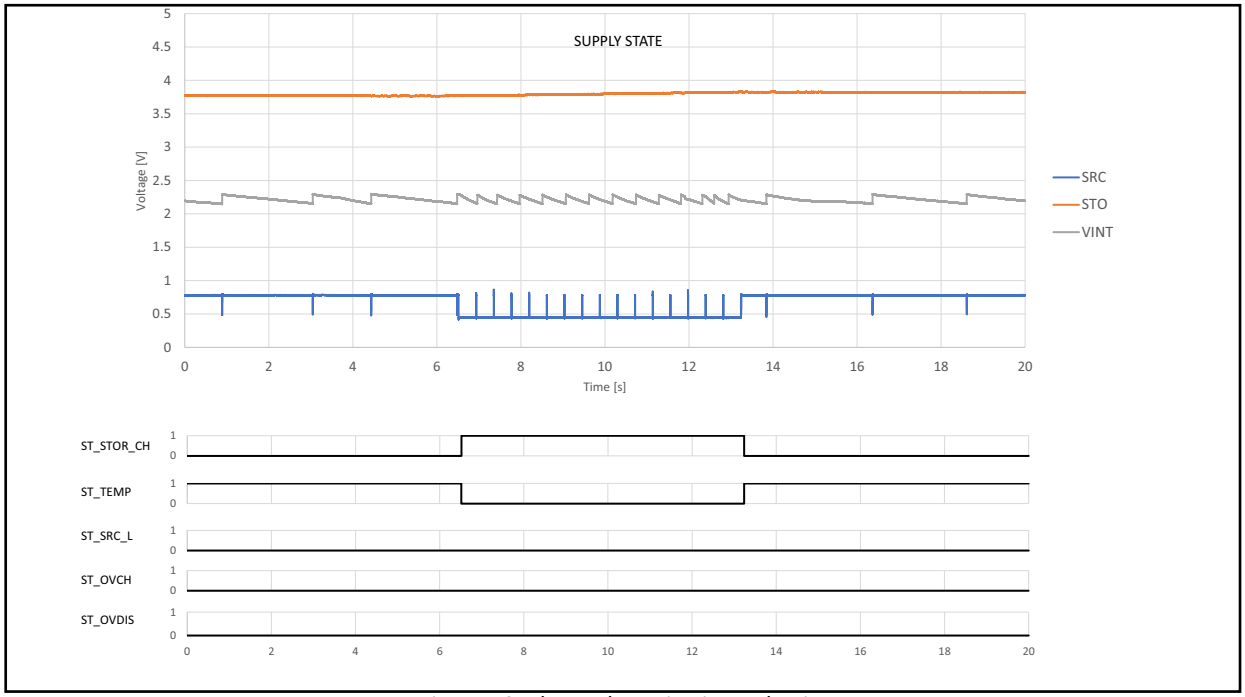

Figure 19: Thermal Monitoring Behavior

STO_CFG[2:0] = HHH, R_MPP[2:0] = LHH, T_MPP[1:0] = HL, storage element: capacitor (10 mF) pre-charged to 3 V, SRC: current source 5 mA with voltage compliance (0.8 V)(stop after ~5 sec), DIS_STO_CH = GND, KEEP_ALIVE = H. The temperature is lower than 0°C before 6.5 s and after 13.2 s.

12. Package Information

12.1. Wafer Level Chip Scale Package (WLCSP16 2x2mm)

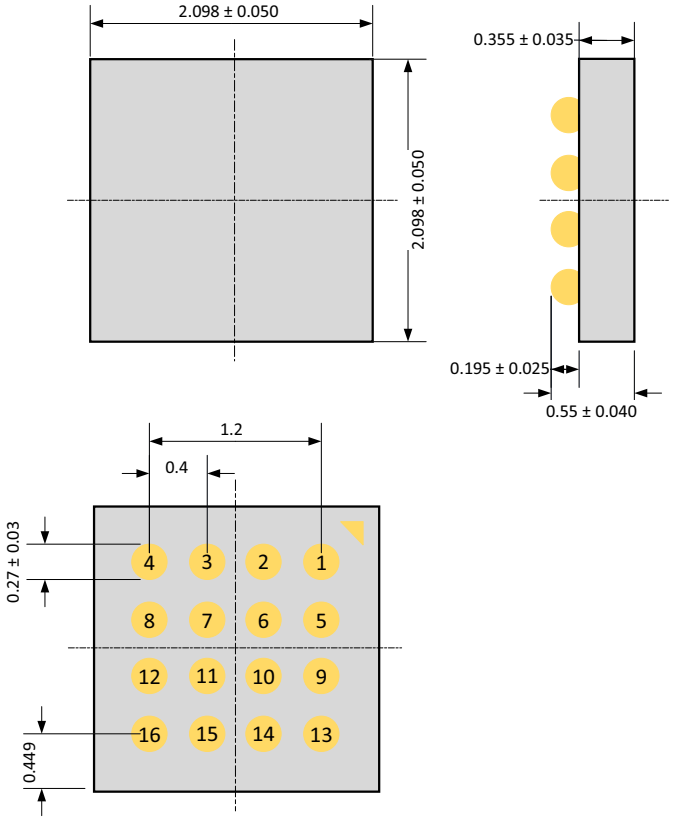

Figure 20: WLCSP16 2x2mm

12.2. WLCSP16 Board Layout

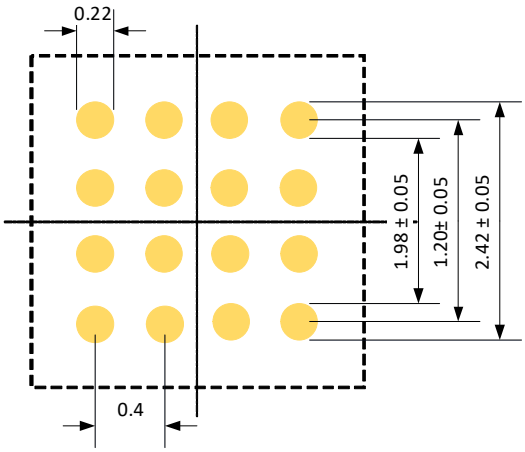

Figure 21: WLCSP16 board layout

12.3. Plastic Quad Flatpack No-lead (QFN28 4x4mm)

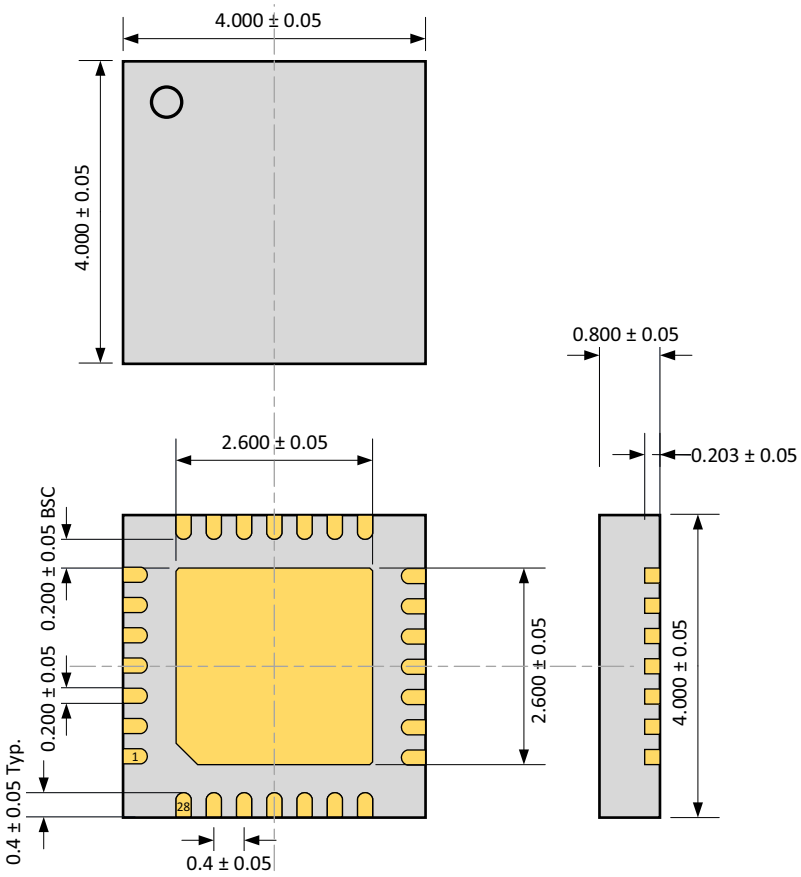

Figure 22: QFN28 4x4 mm

12.4. QFN28 Board Layout

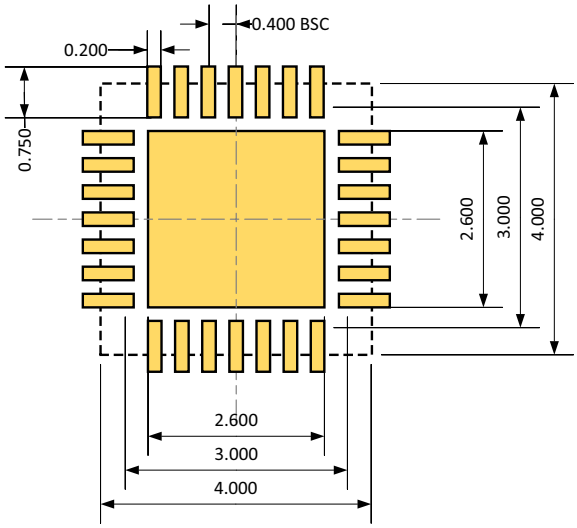

Figure 23: QFN28 4x4 mm board layout

12.5. Thermal Information

Package	θJA	θJC	Unit
WLCSP16	TBD	TBD	°C/W
QFN28	TBD	TBD	°C/W

Table 30: Thermal information

12.6. Material

12.6.1. RoHS Compliance

e-peas product complies with RoHS requirement.

e-peas defines “RoHS” to mean that semiconductor end-products are compliant with RoHS regulation for all 10 RoHS substances.

This applies to silicon, die attached adhesive, gold wire bonding, lead frames, mold compound, and lead finish (pure tin).

12.6.2. REACH Compliance

The component and elements used by e-peas subcontractors to manufacture e-peas PMICs and devices are REACH compliant. For more detailed information, please contact e-peas sales team.

13. Minimum BOM

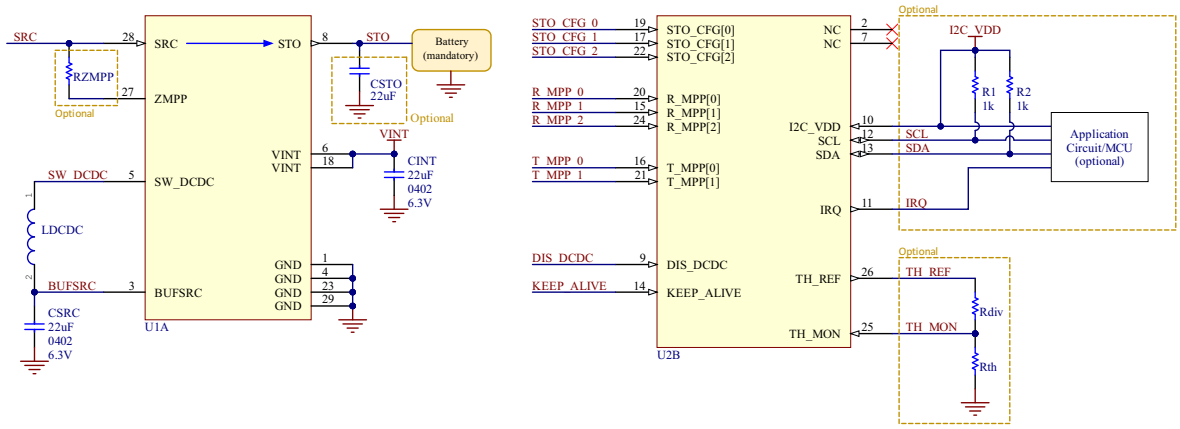

Figure 24: AEM10900 schematic

	Designator	Description	Quantity	Manufacturer	Part number
Mandatory	U1	AEM10900	1	e-peas	order at sales@e-peas.com
	Battery	Battery with 2.8 V min. voltage	1	To be defined by the user	
	LDCDC (AEM10900)	Power inductor 6.8 µH 1.15A 1008	1	TDK	VLS252012HBX-6R8M-1
	CSRC	Ceramic capacitor 22 µF 6.3 V 20% X5R 0402	1	Murata	GRM158R60J226ME01
	CINT	Ceramic capacitor 22 µF 6.3 V 20% X5R 0402	1	Murata	GRM158R60J226ME01
	CSTO	Ceramic capacitor 22 µF 6.3 V 20% X5R 0402	1	Murata	GRM158R60J226ME01
Optional	RZMPP	Resistor for ZMPP functionality	1	To be defined by user	
	R1, R2	Pull-up 1 kΩ Resistors for I²C interface	2	Yageo	AC0603FR-071KL
	Rth	10 kΩ NTC thermistor for temperature monitoring	1	Murata	NCP15XH103J03RC
	Rdiv	Resistor 22 kΩ 1%	1	Yageo	PNRC0402FR-0722KL

Table 31: AEM10900 bill of material

14. Layout

The following Figures are showcasing layout examples of the AEM10900.

The following guidelines must be applied for best performances:

- Make sure that ground and power signals are routed with large tracks. If an internal ground plane is used, place via as close as possible to the components, especially for decoupling capacitors.
- Reactive components related to the boost converter must be placed as close as possible to the corresponding pins (SWDCDC, BUFSRC and STO), and be routed with large tracks/polygons.
- PCB track capacitance must be reduced as much as possible on the boost converter switching node SWDCDC. This is done as follows:
  - Keep the connection between the SWDCDC pin and the inductor short.
  - Remove the ground and power planes under the SWDCDC node. The polygon on the opposite external layer may also be removed.
  - Increase the distance between SWDCDC and the ground polygon on the external PCB layer where the AEM10900 is mounted.
- PCB track capacitance must be reduced as much as possible on the TH_REF node. Same principle as for SWDCDC may be applied.

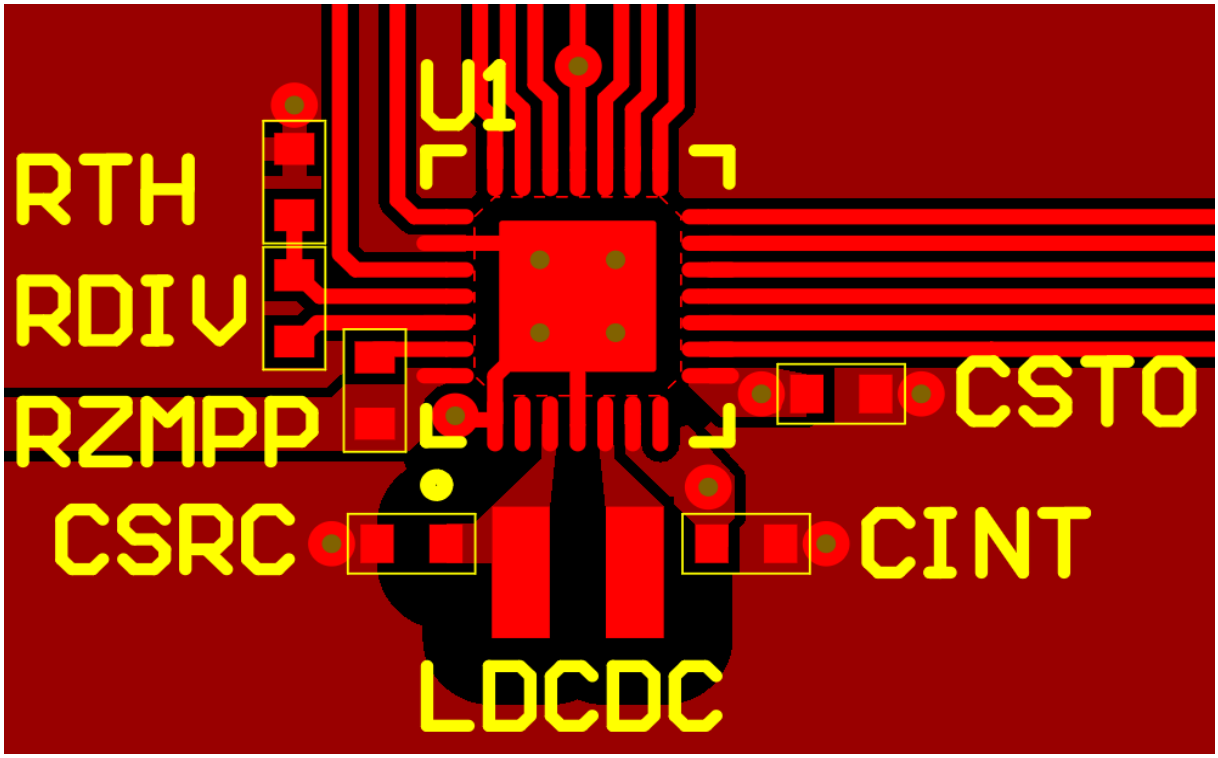

Figure 25: AEM10900 QFN28 layout example

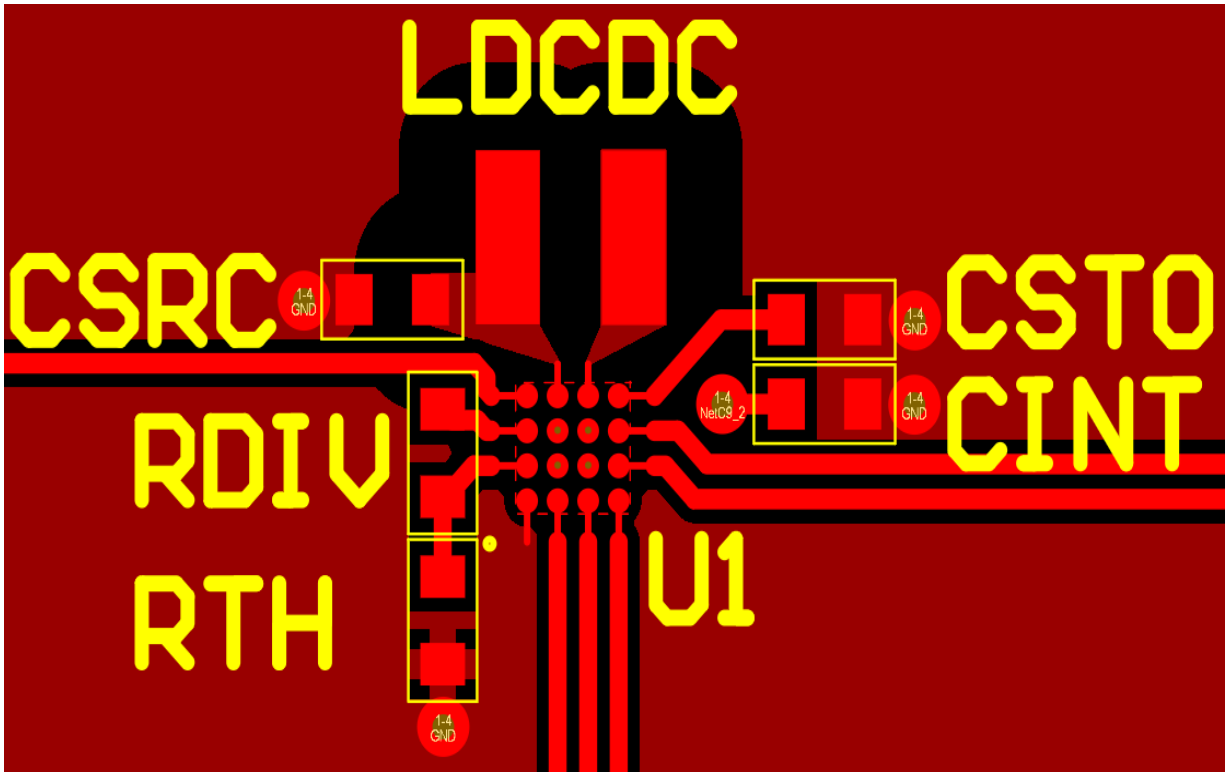

Figure 26: AEM10900 WLCSP16 layout example

15. Glossary

V_{STO}

Voltage at STO pin.

$V_{SRC,CS}$

Minimum source voltage required for cold start.

V_{SRC}

Voltage at SRC pin.

V_{OVDIS}

Overdischarge voltage at STO pin.

V_{OVCH}

Overcharge voltage at STO pin.

V_{OC}

Open-circuit voltage of the harvester connected to the SRC pin.

V_{MPP}

Target regulation voltage on SRC when extracting power.

V_{INT}

AEM10900 internal circuit voltage supply.

$V_{INT,CS}$

Minimum voltage on VINT to allow the AEM10900 to switch from RESET STATE to SENSE STO STATE.

$P_{SRC,CS}$

Minimum power available on SRC for the AEM10900 to coldstart.

$I_{QSUPPLY}$

Quiescent current on VINT when the AEM10900 is in SUPPLY STATE.

I_{QSLEEP}

Quiescent current on VINT when the AEM10900 is in SLEEP STATE.

I_{QSTO}

Quiescent current on STO when Keep-alive functionality is disabled.

I_{QSTO}

Quiescent current on STO when Keep-alive functionality is disabled.

I_{SRC}

Current drawn at the SRC pin.

R_{DIV}

Resistor that creates a resistive voltage divider with R_{TH}.

C_{INT}

VINT pin decoupling capacitor.

C_{SRC}

BUFSRC pin decoupling capacitor.

L_{DCDC}

DCDC converter inductor.

R_{SCL} / R_{SDA}

Respectively, I^2C SCL and SDA pin pull-up resistors.

R_{ZMPP}

Resistor that defines the AEM10900 DCDC converter input resistance when used in ZMPP mode.

T_{MPPT}

Maximum power point tracking sampling period.

T_{VOC}

Duration of the SRC open circuit voltage evaluation.

16. Revision History

Revision	Date	Description
1.0	April, 2021	Creation of the document.
1.1	April, 2021	- Modification of SRC_DATA register value table - Added performance and typical applications
1.2	August, 2022	- Change name of the register and field for the I²C Communication - Change the Package and the pinout for the WLCSP package

1.3	January, 2023	- Global layout update.
		- First page full rework.
		- Introduction: added details on cold start power and SRC extracting range.
		- Typical electrical characteristics:
		  - Cold start voltage vs. MPP voltage.
		  - Cold start power depending on keep-alive enabling.
		- Recommended operating conditions: refined LDCDC value range.
		- MPPT description rework.
		- Keep-alive description improved.
		- IRQ pin: added dedicated section.
		- States description improved.
		- Configuration by pin/registers: clarified.
		- DIS_STO_CH: added dedicated section.
		- Register descriptions: added register names in section titles and improved tables layout.
		- Keep-alive register: added note.
		- Improved register descriptions:
		  - IRQEN.I2CRDY.
		  - IRQFLG.I2CRDY.
		- External inductor informations: improved.
		- Typical application circuits: improved schematics aesthetics.
		- Improved performance graphs aesthetics.
		- Quiescent current graph: improved aesthetics.
		- Moved “Minimum BOM” section outside “Package” section.
		- Added glossary.
		- Explanations about CSTO influence on efficiency.

1.4	February, 2024	- Thermal pad (back plane) renamed as pin 29. - Small fixes
1.5	August, 2024	- Small fixes.
1.6	September, 2024	- Corrected typos and improved some sentences structure.

Table 32: Revision history